Preliminary Datasheet





RL78/G1A

RENESAS MCU

R01DS0151EJ0001 Rev.0.01 2011.12.26

Combines Multi-channel 12-Bit A/D Converter, True Low Power Platform (as low as 66 μ A/MHz, and 0.57 μ A for RTC + LVD), 1.6 V to 3.6 V operation, 16 to 64 Kbyte Flash, 41 DMIPS at 32 MHz

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 1.6 V to 3.6 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.57 μA
- Snooze: T.B.D.
- Operating: 66 μA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction Execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC Architecture (Harvard) with 3-stage pipeline
- Multiply Signed & Unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Code Flash Memory

- Density: 16 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data Flash with background operation
- Data flash size: 4 KB
- Erase Cycles: 1 Million (typ.)
- Erase/programming voltage: 1.8 V to 3.6 V

RAM

- 2 KB to 4 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- \bullet 32 MHz with +/- 1% accuracy over voltage (1.8 V to 3.6 V) and temperature (-20 °C to +85 °C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 4 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 12 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

Multiple Communication Interfaces

- Up to 6 x I2C master
- Up to 1 x I2C multi-master
- Up to 6 x CSI/SPI (7-, 8-bit)
- Up to 3 x UART (7-, 8-, 9-bit)
- Up to 1 x LIN

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval Timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Rich Analog

- ADC: Up to 28 channels, 12-bit resolution, 3.375 μs conversion time
- Supports 1.6 V
- Internal voltage reference (1.45 V)
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM write protection
- SFR write protection
- Illegal memory access detection
- · Clock stop/ frequency detection
- ADC self-test

General Purpose I/O

- 3.6 V tolerant, high-current (up to 20 mA per pin)
- Open-Drain, Internal Pull-up support

Operating Ambient Temperature

• Standard: -40 °C to +85 °C

Package Type and Pin Count

From 3 mm x 3 mm to 10 mm x 10 mm

QFP: 48, 64 QFN: 32, 48 LGA: 25 BGA: 64

1. OUTLINE

O ROM, RAM capacities

| Flash | Data | RAM | | RL78 | 3/G1A | |
|----------|-------|--------------|----------|----------|----------|----------|
| ROM | flash | | 25 pins | 32 pins | 48 pins | 64 pins |
| 64 KB | 4 KB | 4 KB Note | R5F10E8E | R5F10EBE | R5F10EGE | R5F10ELE |
| 48 KB | 4 KB | 3 KB | R5F10E8D | R5F10EBD | R5F10EGD | R5F10ELD |
| 32 KB | 4 KB | 2 KB | R5F10E8C | R5F10EBC | R5F10EGC | R5F10ELC |
| 16 KB | 4 KB | 2 KB | R5F10E8A | R5F10EBA | R5F10EGA | _ |

Note This is about 3 KB when the self-programming function and data flash function are used.

1.2 Ordering Information

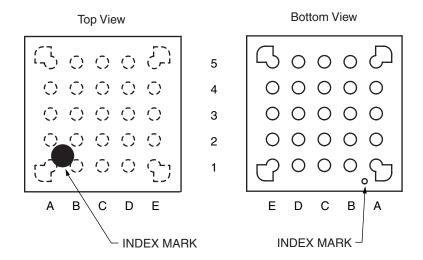
• Flash memory version (lead-free product)

| Pin count | Package | Data flash | Part Number |
|-----------|--|------------|--|
| 25 pins | 25-pin plastic FLGA (3 × 3) | Mounted | R5F10E8AALA, R5F10E8CALA, R5F10E8DALA, R5F10E8EALA |
| 32 pins | 32-pin plastic WQFN (fine pitch) (5 × 5) | Mounted | R5F10EBAANA, R5F10EBCANA, R5F10EBDANA, R5F10EBEANA |
| 48 pins | 48-pin plastic LQFP (fine pitch) (7 × 7) | Mounted | R5F10EGAAFB, R5F10EGCAFB, R5F10EGDAFB, R5F10EGEAFB |
| | 48-pin plastic WQFN (7 × 7) | Mounted | R5F10EGAANA, R5F10EGCANA, R5F10EGDANA, R5F10EGEANA |
| 64 pins | 64-pin plastic LQFP (fine pitch) (10 × 10) | Mounted | R5F10ELCAFB, R5F10ELDAFB, R5F10ELEAFB |
| | 64-pin plastic FBGA (4 × 4) | Mounted | R5F10ELCABG, R5F10ELDABG, R5F10ELEABG |

1.3 Pin Configuration (Top View)

1.3.1 25-pin products

• 25-pin plastic FLGA (3 × 3)



| | Α | В | С | D | E | |
|---|-------------------|-----------------|---|---|-----------------------------------|---|
| 5 | P40/TOOL0 | RESET | P03/ANI16/ RxD1/TO00/ (KR1) | P23/ANI3/ (KR3) | AVss | 5 |
| 4 | P122/X2/ EXCLK | P137/INTP0 | P02/ANI17/ TxD1/TI00/ (KR0) | P22/ANI2/ (KR2) | AV _{DD} | 4 |
| 3 | P121/X1 | V _{DD} | P21/ANI1/ AVREFM | P11/ANI20/ SI00/SDA00/ RxD0/ TOOLRxD | P10/ANI18/ SCK00/SCL00 | 3 |
| 2 | REGC | Vss | P30/ANI27/ SCK11/SCL11/ INTP3 | P51/ANI25/ SO11/INTP2 | P50/ANI26/ SI11/SDA11 INTP1 | 2 |
| 1 | P60/SCLA0 | P61/SDAA0 | P31/ANI29/TI03/ TO03/PCLBUZ0 /INTP4 | P12/ANI21/ SO00/TxD0/ TOOLTxD | P20/ANI0/ AVREFP | 1 |
| | A | В | С | D | E | • |

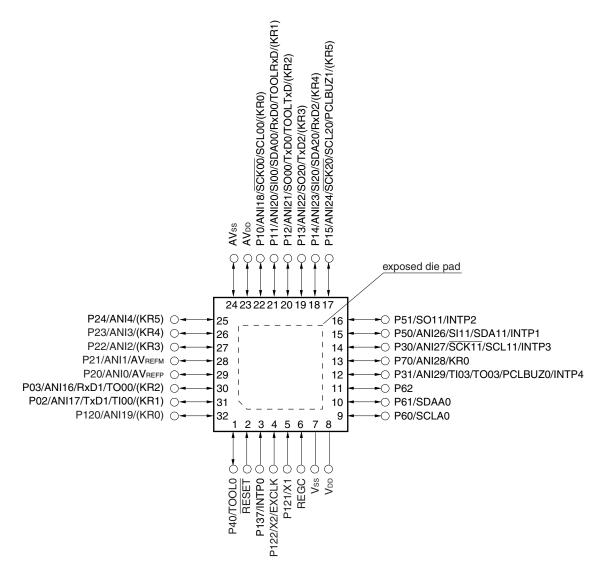
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.2 32-pin products

• 32-pin plastic WQFN (fine pitch) (5 × 5)



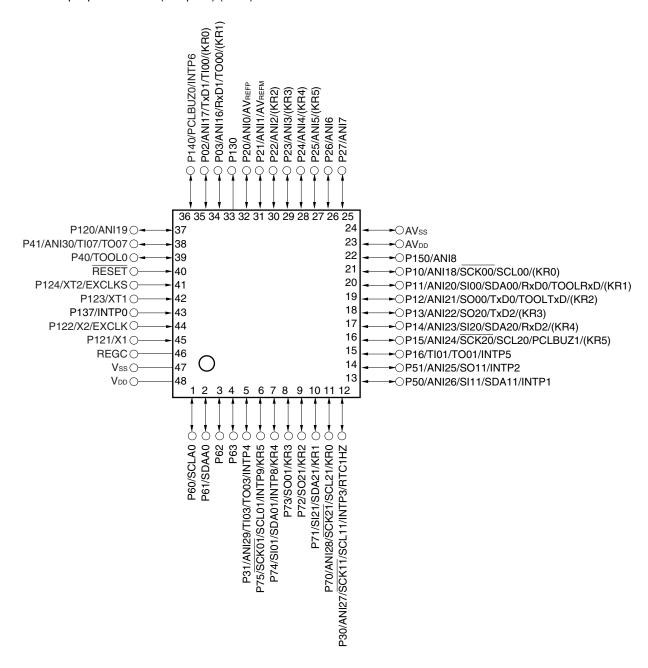
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.3 48-pin products

• 48-pin plastic LQFP (fine pitch) (7 × 7)

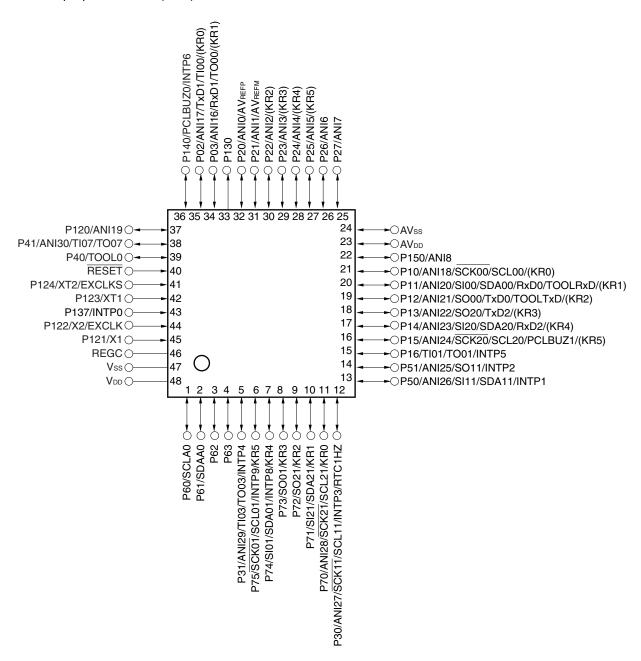


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

• 48-pin plastic WQFN (7 × 7)



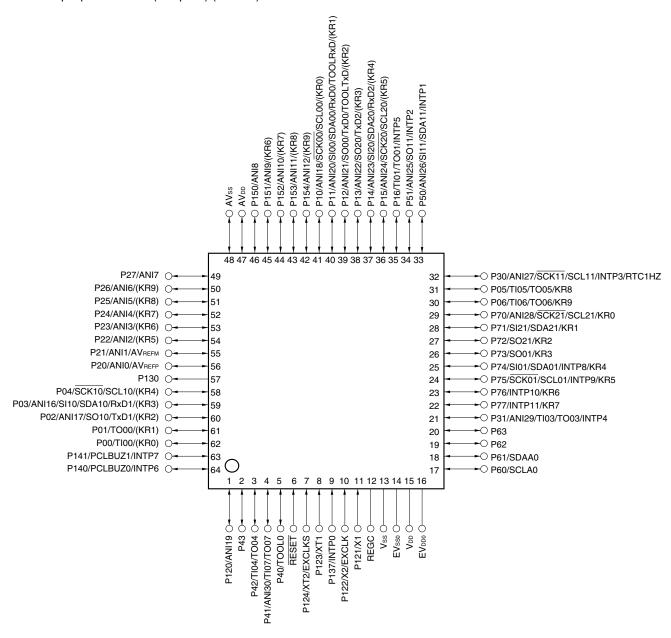
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

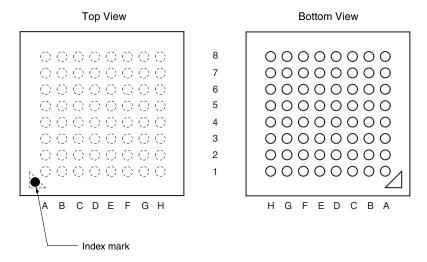
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• 64-pin plastic LQFP (fine pitch) (10 × 10)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDDO pins and connect the Vss and EVss0pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

• 64-pin plastic FBGA (4 × 4)



| Pin No. | Name | Pin No. | Name | Pin No. | Name | Pin No. | Name |
|---------|--|---------|---------------------------------------|---------|---|---------|-------------------------------|
| A1 | P05/TI05/TO05/KR8 | C1 | P51/ANI25/SO11 /INTP2 | E1 | P153/ANI11/(KR8) | G1 | AV _{DD} |
| A2 | P30/ANI27/SCK11 /SCL11/INTP3 /RTC1HZ | C2 | P71/SI21/SDA21/KR1 | E2 | P154/ANI12/(KR9) | G2 | P25/ANI5/(KR8) |
| A3 | P70/ANI28/SCK21 /SCL21/KR0 | C3 | P74/SI01/SDA01 /INTP8/KR4 | E3 | P10/ANI18/SCK00 /SCL00/(KR0) | G3 | P24/ANI4/(KR7) |
| A4 | P75/SCK01/SCL01 /INTP9/KR5 | C4 | P16/TI01/TO01/INTP5 | E4 | P11/ANI20/SI00 /SDA00/RxD0 /TOOLRxD/(KR1) | G4 | P22/ANI2/(KR5) |
| A5 | P77/INTP11/KR7 | C5 | P15/ANI24/SCK20 /SCL20/(KR5) | E5 | P03/ANI16/SI10 /SDA10/RxD1/(KR3) | G5 | P130 |
| A6 | P61/SDAA0 | C6 | P63 | E6 | P41/ANI30/TI07/TO07 | G6 | P02/ANI17/SO10/TxD1 /(KR2) |
| A7 | P60/SCLA0 | C7 | Vss | E7 | RESET | G7 | P00/TI00/(KR0) |
| A8 | EV _{DD0} | C8 | P121/X1 | E8 | P137/INTP0 | G8 | P124/XT2/EXCLKS |
| B1 | P50/ANI26 /SI11 /SDA11/INTP1 | D1 | P13/ANI22/SO20 /TxD2/(KR3) | F1 | P150/ANI8 | H1 | AVss |
| B2 | P72/SO21/KR2 | D2 | P06/TI06/TO06/KR9 | F2 | P151/ANI9/(KR6) | H2 | P27/ANI7 |
| В3 | P73/S001/KR3 | D3 | P12/ANI21/SO00 /TxD0/TOOLTxD/(KR2) | F3 | P152/ANI10/(KR7) | НЗ | P26/ANI6/(KR9) |
| B4 | P76/INTP10/KR6 | D4 | P14/ANI23/SI20/ SDA20/RxD2/(KR4) | F4 | P21/ANI1/AVREFM | H4 | P23/ANI3/(KR6) |
| B5 | P31/ANI29/TI03/TO03 /INTP4 | D5 | P42/TI04/TO04 | F5 | P04/SCK10/SCL10 /(KR4) | H5 | P20/ANI0/AVREFP |
| B6 | P62 | D6 | P40/TOOL0 | F6 | P43 | H6 | P141/PCLBUZ1/INTP7 |
| B7 | V _{DD} | D7 | REGC | F7 | P01/TO00/(KR1) | H7 | P140/PCLBUZ0/INTP6 |
| B8 | EVsso | D8 | P122/X2/EXCLK | F8 | P123/XT1 | H8 | P120/ANI19 |

- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

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1. OUTLINE

1.4 Pin Identification

ANI0 to ANI12, PCLBUZ0, PCLBUZ1: Programmable clock output/buzzer ANI16 to ANI30: Analog input output AV_{DD}: REGC: Regulator capacitance Analog power supply AVss: Analog ground RESET: Reset AVREFM: A/D converter reference RTC1HZ: Real-time clock correction clock potential (- side) input (1 Hz) output AVREFP: A/D converter reference RxD0 to RxD2: Receive data potential (+ side) input SCK00, SCK01, SCK10, EV_{DD0}: Power supply for port SCK11, SCK20, SCK21: Serial clock input/output EVsso: Ground for port SCLA0, SCL00, SCL01, EXCLK: External clock input (main SCL10, SCL11, SCL20, SCL21: system clock) Serial clock input/output External clock input (sub **EXCLKS:** SDAA0, SDA00, SDA01, system clock) SDA10, SDA11, SDA20, INTP0 to INTP11: External interrupt input SDA21: Serial data input/output KR0 to KR9: Key return SI00, SI01, SI10, SI11, P00 to P06: Port 0 SI20, SI21: Serial data input P10 to P16: Port 1 SO00, SO01, SO10, P20 to P27: Port 2 SO11, SO20, SO21: Serial data output P30, P31: Port 3 TI00, TI01, TI03 to TI07: Timer input P40 to P43: Port 4 TO00, TO01, P50, P51: TO03 to TO07: Port 5 Timer output P60 to P63: Port 6 TOOL0: Data input/output for tool P70 to P77: Port 7 TOOLRxD, TOOLTxD: Data input/output for external device

P120 to P124: Port 12 TxD0 to TxD2: Transmit data

P130, P137: Port 13 VDD: Power supply

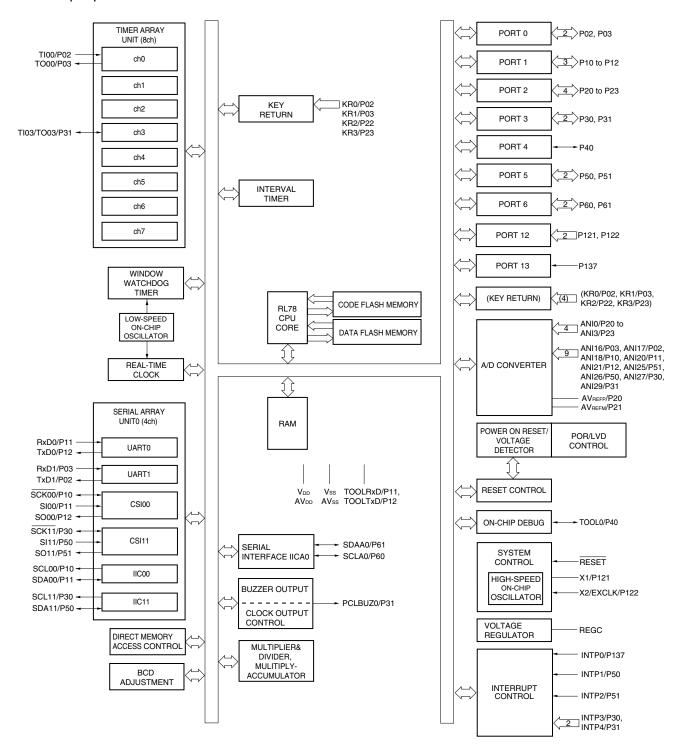
P140, P141: Port 14 Vss: Ground
P150 to P154: Port 15 X1, X2: Crystal oscillator (main system clock)

XT1, XT2: Crystal oscillator (subsystem clock)

Specifications in this document are tentative and subject to change.

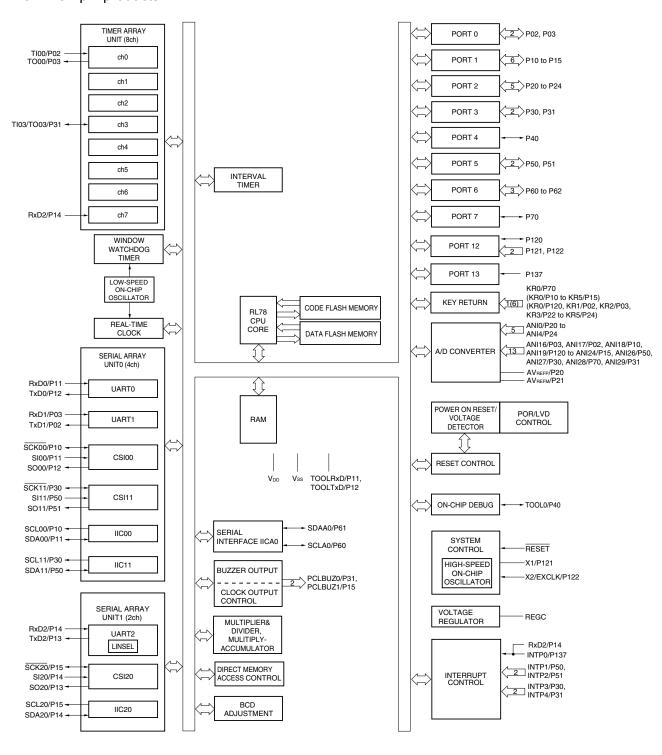
1.5 Block Diagram

1.5.1 25-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

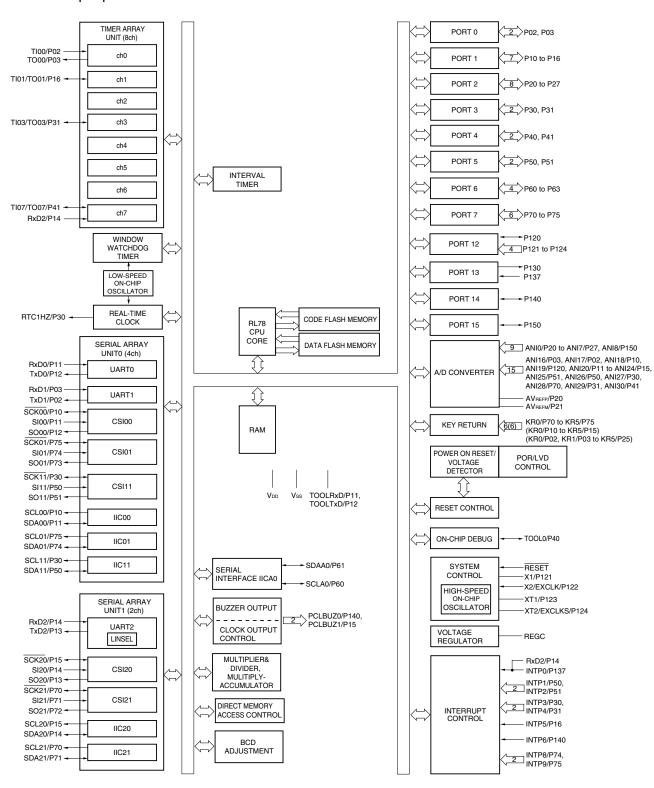
RL78/G1A



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

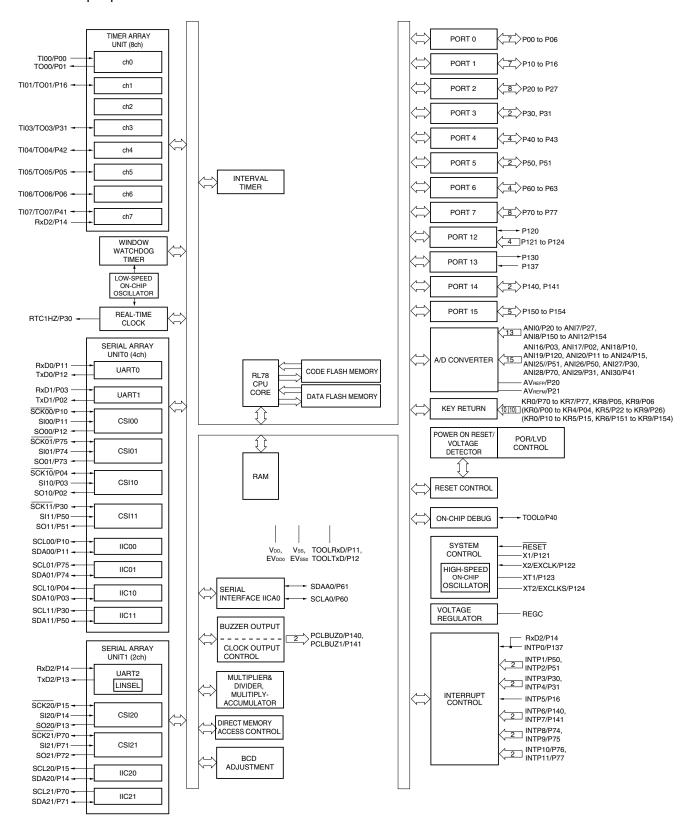
Specifications in this document are tentative and subject to change.

1.5.3 48-pin products



Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.5.4 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.6 Outline of Functions

(1/2)

| | | | | | (1/2) | | |
|--------------------------|--|--|---|---|---------------------------------------|--|--|
| | Item | 25-pin | 32-pin | 48-pin | 64-pin | | |
| | | R5F10E8x | R5F10EBx | R5F10EGx | R5F10ELx | | |
| Code flash m | emory (KB) | 16 to 64 | 16 to 64 | 16 to 64 | 32 to 64 | | |
| Data flash me | emory (KB) | 4 | 4 | 4 | 4 | | |
| RAM (KB) | | 2 to 4 ^{Note1} | 2 to 4 ^{Note1} | 2 to 4 ^{Note1} | 2 to 4 ^{Note1} | | |
| Memory space | ce | 1 MB | | | | | |
| Main system clock | High-speed system clock | | - | stem clock input (EXCLK = 1.8 to 2.7 V, 1 to 4 MH | | | |
| | High-speed on-chip oscillator | 2.4 to 3.6 V), Low-speed | High-speed operation: 1 to 32 MHz (V_{DD} = 2.7 to 3.6 V), High-speed operation: 1 to 16 MHz (2.4 to 3.6 V), Low-speed operation: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), Low-voltage operation: 1 MHz (V_{DD} = 1.6 to 3.6 V) | | | | |
| Subsystem c | lock | | _ | XT1 (crystal) oscillation clock input (EXCLKS) | | | |
| | | | | 32.768 kHz (TYP.): VDD | = 1.6 to 3.6 V | | |
| Low-speed o | n-chip oscillator | 15 kHz (TYP.): V _{DD} = 1.0 | 6 to 3.6 V | | | | |
| General-purpose register | | 8 bits × 32 registers (8 bits × 8 registers × 4 banks) | | | | | |
| Minimum inst | truction execution time | 0.03125 μs (High-speed | d on-chip oscillator: fin = 3 | 32 MHz operation) | | | |
| | | 0.05 μ s (High-speed sys | stem clock: fmx = 20 MHz | operation) | | | |
| | | | _ | 30.5 μ s (Subsystem clock: fsuB = 32.768 kHz operation) | | | |
| Instruction se | et | Multiplication (8 bits | r/logical operation (8/16 t \times 8 bits) | pits) reset, test, and Boolean | operation), etc. | | |
| I/O port | Total | 19 | 26 | 42 | 56 | | |
| | CMOS I/O | 14 | 20 | 32 | 46 | | |
| | CMOS input | 3 | 3 | 5 | 5 | | |
| | CMOS output | - | - | 1 | 1 | | |
| | N-ch open-drain I/O (6 V tolerance) | 2 | 3 | 4 | 4 | | |
| Timer | 16-bit timer | | 8 cha | annels | | | |
| | Watchdog timer | | 1 ch | annel | | | |
| | Real-time clock (RTC) | - | | 1 ch | annel | | |
| | Interval timer (IT) | | 1 ch | annel | | | |
| | Timer output | 2 channels (PWM output | ts: 1 Note 2) | 4 channels (PWM outputs: 3 Note 2) | 7 channels (PWM outputs: 6 Note 2) | | |
| | RTC output | | = | 1 • 1 Hz (subsystem clock: fsub = 32.768 kHz or) | | | |

Notes 1. In the case of the 4 KB, this is about 3 KB when the self-programming function and data flash function are used.

2. The number of outputs varies, depending on the setting.

(2/2)

| | | | | | (2/2) | | |
|------------------------------------|----------------------|---|---|-------------|-------------|--|--|
| Ite | m | 25-pin | 32-pin | 48-pin | 64-pin | | |
| | | R5F10E8x | R5F10EBx | R5F10EGx | R5F10ELx | | |
| Clock output/buzz | er output | 1 | 2 | 2 | 2 | | |
| | | 2.5 MHz, 5 MHz, 10 M | 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 (Subsystem clock: fsub = 32.768 kHz operation) | | | | |
| 8/12-bit resolution | A/D converter | 13 channels | 18 channels | 24 channels | 28 channels | | |
| Serial interface | | [25-pin products] | | | | | |
| | | [32-pin products] CSI: 1 channel/UAR CSI: 1 channel/UAR CSI: 1 channel/UAR [48-pin products] CSI: 2 channels/UAR CSI: 1 channel/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR CSI: 2 channels/UAR | GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel In products] GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels GI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel GI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels In products] GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels GI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels | | | | |
| | | | 1 | 1 | 1 | | |
| Multiplier and divider/multiply-ad | I ² C bus | 1 channel 1 channel 1 channel 1 channel 1 channel | | | | | |
| | | • 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) | | | | | |
| DMA controller | | 2 channels | | | | | |
| Vectored | Internal | 24 | 27 | 27 | 27 | | |
| interrupt sources | External | 6 | 6 | 10 | 13 | | |
| Key interrupt | | 0 ch (4 ch) Note 1 | 1 ch (6 ch) Note 1 | 6 ch | 10 ch | | |
| Reset | | Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note 2 Internal reset by RAM parity error Internal reset by illegal-memory access | | | | | |
| Power-on-reset ci | rcuit | Power-on-reset: 1. Power-down-reset: 1. | 51 ±0.03 V 50 ±0.03 V | | | | |
| Voltage detector | | 1.63 V to 3.06 V (12 sta | ages) | | | | |
| On-chip debug fu | nction | Provided | | | | | |
| Power supply volt | age | V _{DD} = 1.6 to 3.6 V | | | | | |
| Operating ambier | t temperature | T _A = -40 to +85 °C | | | | | |

- Notes 1. Can be used by the Peripheral I/O redirection register (PIOR).
 - The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

- Cautions 1. These specifications show target values, which may change after device evaluation.
 - 2. The RL78/G1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 3. The pins mounted depend on the product. Refer to 1.3.1 25-pin products to 1.3.4 64-pin products.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) (1/2)

| Parameter | Symbols | Conditions | Ratings | Unit |
|------------------------|-------------------|--|--|------|
| Supply voltage | V _{DD} | | -0.5 to +6.5 | V |
| | EV _{DD0} | $EV_{DD0} \leq V_{DD}$ | -0.5 to +6.5 | V |
| | AV _{DD} | $AV_{DD0} \leq V_{DD}$ | -0.5 to +4.6 | V |
| | Vss | | -0.5 to +0.3 | V |
| | EV _{SS0} | | -0.5 to +0.3 | V |
| | AVss | | -0.5 to +0.3 | V |
| REGC pin input voltage | VIREGC | REGC | -0.3 to $+2.8$ and -0.3 to V_{DD} $+0.3^{Note 1}$ | V |
| Input voltage | VII | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141 | -0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2} | ٧ |
| | V _{I2} | P60 to P63 (N-ch open-drain) | -0.3 to +6.5 | V |
| | Vı3 | P121 to P124, P137, EXCLK, EXCLKS, RESET | -0.3 to V _{DD} +0.3 ^{Note 2} | V |
| | VI4 | P20 to P27, P150 to P154 | -0.3 to AV _{DD} +0.3 ^{Note 3} | V |
| Output voltage | V ₀₁ | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P130, P140, P141 | -0.3 to EV _{DD0} +0.3 ^{Note 2} | ٧ |
| | V _{O2} | P20 to P27, P150 to P154 | -0.3 to V _{DD} +0.3 Note 2 | V |
| Analog input voltage | V _{Al1} | ANI16 to ANI30 | -0.3 to EV _{DD0} +0.3 Note 2 | ٧ |
| | V _{Al2} | ANI0 to ANI12 | -0.3 to AV _{DD} +0.3 Note 2 | V |

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum ratinwg of the REGC pin. Do not use this pin with voltage applied to it.

- Must be 6.5 V or lower. 2.
- Must be 4.6 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Absolute Maximum Ratings (TA = 25°C) (2/2)

| Parameter | Symbols | | Conditions | Ratings | Unit |
|----------------------|--------------------------|-----------------------------|--|-------------|------|
| Output current, high | Іон1 | Per pin | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141 | -40 | mA |
| | | Total of all pins -170 mA | P00 to P04, P40 to P43, P120, P130, P140, P141 | -70 | mA |
| | | | P05, P06, P10 to P16, P30, P31, P50, P51, P70 to P77, | -100 | mA |
| | І ОН2 | Per pin | P20 to P27, P150 to P154 | -0.1 | mA |
| | | Total of all pins | | -1.3 | mA |
| Output current, low | lo _{L1} Per pin | | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P130, P140, P141 | 40 | mA |
| | | Total of all pins 170 mA | P00 to P04, P40 to P43, P120, P130, P140, P141 | 70 | mA |
| | | | P05, P06, P10 to P16, P30, P31, P50, P51, P60 to P63, P70 to P77 | 100 | mA |
| | lo _{L2} | Per pin | P20 to P27, P150 to P154 | 0.4 | mA |
| | | Total of all pins | | 6.4 | mA |
| Operating ambient | TA | In normal operati | on mode | -40 to +85 | °C |
| temperature | | In flash memory | programming mode | | |
| Storage temperature | T _{stg} | | | -65 to +150 | °C |

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 Main system clock oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Resonator | Recommended Circuit | Parameter | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------|------------------------|--------------------------------|--------------------------------|------|------|------|------|
| Ceramic resonator | V _{SS} X1 X2 | X1 clock oscillation | $2.7~V \leq V_{DD} \leq 3.6~V$ | 1.0 | | 20.0 | MHz |
| | Rd { | frequency (fx) ^{Note} | $1.8~V \leq V_{DD} < 2.7~V$ | 1.0 | | 8.0 | MHz |
| | C1 C2 7 | | $1.6~V \le V_{DD} < 1.8~V$ | 1.0 | | 4.0 | MHz |
| Crystal resonator | | X1 clock oscillation | $2.7~V \leq V_{DD} \leq 3.6~V$ | 1.0 | | 20.0 | MHz |
| | Vss X1 X2 | frequency (fx) ^{Note} | $1.8~V \leq V_{DD} < 2.7~V$ | 1.0 | | 8.0 | MHz |
| | C1= C2= | | $1.6~V \le V_{DD} < 1.8~V$ | 1.0 | | 4.0 | MHz |

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Cautions 1. When using the X1 oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- Keep the wiring length as short as possible.
- Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as Vss.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- Do not fetch signals from the oscillator.
- 2. Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.



2.2.2 On-chip oscillator characteristics

 $(T_A = -20 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Oscillators | Parameters | Con | ditions | MIN. | TYP. | MAX. | Unit |
|--|------------|---------------------------------|-----------------|-------|-------|-------|------|
| High-speed on-chip | fıн | $1.8~V \leq V_{DD} \leq 3.6~V$ | 32 MHz selected | 31.68 | 32.00 | 32.32 | MHz |
| oscillator clock frequency Note | | | 24 MHz selected | 23.76 | 24.00 | 24.24 | MHz |
| | | | 16 MHz selected | 15.84 | 16.00 | 16.16 | MHz |
| | | | 12 MHz selected | 11.88 | 12.00 | 12.12 | MHz |
| | | | 8 MHz selected | 7.92 | 8.00 | 8.08 | MHz |
| | | | 4 MHz selected | 3.96 | 4.00 | 4.04 | MHz |
| | | | 1 MHz selected | 0.99 | 1.00 | 1.01 | MHz |
| | | 1.6 V ≤ V _{DD} < 1.8 V | 32 MHz selected | 30.40 | 32.00 | 33.60 | MHz |
| | | | 24 MHz selected | 22.80 | 24.00 | 25.20 | MHz |
| | | | 16 MHz selected | 15.20 | 16.00 | 16.80 | MHz |
| | | | 12 MHz selected | 11.40 | 12.00 | 12.60 | MHz |
| | | | 8 MHz selected | 7.60 | 8.00 | 8.40 | MHz |
| | | | 4 MHz selected | 3.80 | 4.00 | 4.20 | MHz |
| | | | 1 MHz selected | 0.95 | 1.00 | 1.05 | MHz |
| Low-speed on-chip oscillator clock frequency | fıL | | | 12.75 | 15 | 17.25 | kHz |

 $(T_A = -40 \text{ to } -20^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| (1X = -+0 to -20 0, 1.0 | $A = -40 (0 - 20 C, 1.0 V \le EVDDU \le VDD \le 3.0 V, VSS = EVSSU = 0 V)$ | | | | | | | | | |
|---------------------------------|--|---------------------------------|-----------------|-------|-------|-------|------|--|--|--|
| Oscillators | Parameters | Con | ditions | MIN. | TYP. | MAX. | Unit | | | |
| High-speed on-chip | fıн | $1.8~V \leq V_{DD} \leq 3.6~V$ | 32 MHz selected | 31.52 | 32.00 | 32.48 | MHz | | | |
| oscillator clock frequency Note | | | 24 MHz selected | 23.64 | 24.00 | 24.36 | MHz | | | |
| | | | 16 MHz selected | 15.76 | 16.00 | 16.24 | MHz | | | |
| | | | 12 MHz selected | 11.82 | 12.00 | 12.18 | MHz | | | |
| | | | 8 MHz selected | 7.88 | 8.00 | 8.12 | MHz | | | |
| | | 1.6 V ≤ V _{DD} < 1.8 V | 4 MHz selected | 3.94 | 4.00 | 4.06 | MHz | | | |
| | | | 1 MHz selected | 0.985 | 1.00 | 1.015 | MHz | | | |
| | | | 32 MHz selected | 30.24 | 32.00 | 33.76 | MHz | | | |
| | | | 24 MHz selected | 22.68 | 24.00 | 25.32 | MHz | | | |
| | | | 16 MHz selected | 15.12 | 16.00 | 16.88 | MHz | | | |
| | | | 12 MHz selected | 11.34 | 12.00 | 12.66 | MHz | | | |
| | | | 8 MHz selected | 7.56 | 8.00 | 8.44 | MHz | | | |
| | | | 4 MHz selected | 3.78 | 4.00 | 4.22 | MHz | | | |
| | | | 1 MHz selected | 0.945 | 1.00 | 1.055 | MHz | | | |
| Low-speed on-chip oscillator | fiL | | | 12.75 | 15 | 17.25 | kHz | | | |
| clock frequency | | | | | | | | | | |

Note This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.2.3 Subsystem clock oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Resonator | Recommended Circuit | Items | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------|----------------------------|---|------------|------|--------|------|------|
| Crystal resonator | Vss XT2 XT1 Rd C4 — C3 — | XT1 clock oscillation frequency (fxt) ^{Note} | | 32 | 32.768 | 35 | kHz |

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.

Cautions 1. When using the XT1 oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- . Keep the wiring length as short as possible.
- Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as Vss.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- . Do not fetch signals from the oscillator.
- 2. The XT1 oscillator is designed as a low-amplitude circuit for reducing power consumption, and is more prone to malfunction due to noise than the X1 oscillator. Particular care is therefore required with the wiring method when the XT1 clock is used.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C} + 16 \text{ V} < \text{FV}_{DD} < 3.6 \text{ V} \text{ Vss} = \text{FV}_{SSO} = 0.0 \text{ V})$

Specifications in this document are tentative and subject to change.

| Items | Symbol | Conditions | | MIN. | TYP. | MAX. | Unit |
|---|--------------|--|-----------------------------------|------|---------------|------------------------|------|
| Output current, high ^{Note 1} | Іон1 | Per pin for P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141 | 1.6 V ≤ EV _{DD0} ≤ 3.6 V | | | -10.0 Note 2 | mA |
| | | Total of P00 to P04, P40 to P43, P120, | $2.7~V \le EV_{DD0} \le 3.6~V$ | | -10.0 -5.0 | | mA |
| | | P130, P140, P141 | 1.8 V ≤ EV _{DD0} < 2.7 V | | | -5.0 | |
| | | (When duty = 70% Note 3) | 1.6 V ≤ EV _{DD0} < 1.8 V | | | -2.5 | mA |
| | | Total of P05, P06, P10 to P16, P30, | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | | | -19.0 | mA |
| | | P31, P50, P51, P70 to P77, | $1.8~V \leq EV_{DD0} < 2.7~V$ | | | -10.0 | mA |
| | | (When duty = 70% Note 3) | $1.6~V \le EV_{DD0} < 1.8~V$ | | | -5.0 | mA |
| | | Total of all pins (When duty = 70% ^{Note 3}) | $1.6~V \le EV_{DD0} \le 3.6~V$ | | | -29.0 | mA |
| | І он2 | Per pin for P20 to P27, P150 to P154 | $1.6~V \leq AV_{DD} \leq 3.6~V$ | | | -0.1 ^{Note 2} | mA |
| | | Total of all pins (When duty = 70% ^{Note 3}) | $1.6~V \le AV_{DD} \le 3.6~V$ | | | -1.3 | mA |

- Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDD, VDD pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor is 70%.

The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(loh \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 50% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(50 \times 0.01) = -14.0$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Cautions 1. P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 do not output high level in N-ch open-drain mode.
 - 2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV}_{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Items | Symbol | Conditions | | MIN. | TYP. | MAX. | Unit |
|-----------------|------------------|--|--|---------|------|-------------|------|
| Output current, | IOL1 | Per pin for P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141 | | Will V. | | 20.0 Note 2 | mA |
| | | Per pin for P60 to P63 | | | | 15.0 Note 2 | mA |
| | | Total of P00 to P04, P40 to P43, | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | | | 15.0 | mA |
| | | P120, P130, P140, P141 (When duty = 70% Note 3) | $1.8~V \leq EV_{DD0} < 2.7~V$ | | | 9.0 | mA |
| | | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$ | | | 4.5 | mA |
| | | P31, P50, P51, P60 to P63, | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | | | 35.0 | mA |
| | | | $1.8~V \le EV_{DD0} < 2.7~V$ | | | 20.0 | mA |
| | | P70 to P77 (When duty = 70% Note 3) | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$ | | | 10.0 | mA |
| | | Total of all pins (When duty = 70% Note 3) | | | | 50.0 | mA |
| | lo _{L2} | Per pin for P20 to P27, P150 to P154 | | | | 0.4 Note 2 | mA |
| | | Total of all pins (When duty = 70% ^{Note 3}) | $1.6~V \leq AV_{DD} \leq 3.6~V$ | | | 5.2 | mA |

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor is 70%.

The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 50% and lol = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(50 \times 0.01) = 14.0 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \ \text{V} \leq \text{AV} \text{DD} \leq 3.6 \ \text{V}, \ 1.6 \ \text{V} \leq \text{EV} \text{DD0} \leq \text{VDD} \leq 3.6 \ \text{V}, \ \text{Vss} = \text{EV} \text{SS0} = 0 \ \text{V})$

| Items | Symbol | Conditions | | MIN. | TYP. | MAX. | Unit |
|------------------------|------------------|--|--|----------------------|------|----------------------|----------|
| Input voltage, high | V _{IH1} | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141 | Normal input buffer | 0.8EV _{DD0} | | EV _{DD0} | V |
| | V _{IH2} | P01, P03, P04, P10, P11, P13 to P16, P43 | TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}$ | 2.0 | | EV _{DD0} | V |
| | | | TTL input buffer $1.6~V \le EV_{DD0} < 3.3~V$ | 1.5 | | EV _{DD0} | V |
| | V _{IH3} | P20 to P27, P150 to P154 | | 0.7AV _{DD} | | AV _{DD} | V |
| | V _{IH4} | P60 to P63 | | 0.7EV _{DD0} | | 6.0 | V |
| | V _{IH5} | P121 to P124, P137, EXCLK, EXCLK | (S, RESET | 0.8V _{DD} | | V _{DD} | V |
| Input voltage, low | V _{IL1} | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141 | Normal input buffer | 0 | | 0.2EV _{DD0} | \ |
| | V _{IL2} | P01, P03, P04, P10, P11, P13 to P16, P43 | TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}$ | 0 | | 0.5 | V |
| | | | TTL input buffer $1.6~V \le EV_{DD0} < 3.3~V$ | 0 | | 0.32 | V |
| | V _{IL3} | P20 to P27, P150 to P154 | | 0 | | 0.3AV _{DD} | V |
| | V _{IL4} | P60 to P63 | | 0 | _ | 0.3EVDD0 | V |
| | V _{IL5} | P121 to P124, P137, EXCLK, EXCLK | (S, RESET | 0 | | 0.2V _{DD} | V |

Cautions 1. The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 is EV_{DD0}, even in the N-ch open-drain mode.

2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} 0 \le \text{V} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

| Items | Symbol | Conditions | | MIN. | TYP. | MAX. | Unit |
|----------------------|------------------|---|---|-------------------------|------|------|------|
| Output voltage, high | V _{OH1} | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, | $2.7~V \leq EV_{\text{DD0}} \leq 3.6~V,$ $I_{\text{OH1}} = -2.0~\text{mA}$ | EV _{DD0} – 0.6 | | | V |
| | | P120, P130, P140, P141 | $\label{eq:loss_loss} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 3.6 \ V, \\ \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$ | EV _{DD0} – 0.5 | | | V |
| | | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$ | EV _{DD0} – 0.5 | | | V |
| | V _{OH2} | P20 to P27, P150 to P154 | $1.6~V \le AV_{DD} \le 3.6~V,$ $I_{OH2} = -100~\mu~A$ | AV _{DD} – 0.5 | | | ٧ |
| Output voltage, low | V _{OL1} | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, | $\label{eq:local_local_local} \begin{split} 2.7 \ V & \leq EV_{\text{DD0}} \leq 3.6 \ V, \\ I_{\text{OL1}} & = 3.0 \ \text{mA} \end{split}$ | | | 0.6 | V |
| | | P120, P130, P140, P141 | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL1} = 1.5~mA$ | | | 0.4 | V |
| | | | $1.8~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL1} = 0.6~mA$ | | | 0.4 | V |
| | | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $\text{IoL}_1 = 0.3 \text{ mA}$ | | | 0.4 | V |
| | V _{OL2} | P20 to P27, P150 to P154 | $1.6~V \leq AV_{DD} \leq 3.6~V,$ $I_{OL2} = 400~\mu~A$ | | | 0.4 | V |
| | V _{OL3} | P60 to P63 | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL3} = 3.0~mA$ | | | 0.4 | V |
| | | | $1.8~V \leq EV_{DD0} \leq 3.6~V,$ $I_{OL3} = 2.0~mA$ | | | 0.4 | V |
| | | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $\text{Iol3} = 1.0 \text{ mA}$ | | | 0.4 | V |

- Caution 1. P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 do not output high level in N-ch open-drain mode.
 - 2. Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} 0 \le \text{V} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

| Items | Symbol | Conditio | ns | | MIN. | TYP. | MAX. | Unit |
|--------------------------------|--------|---|-----------------|---------------------------------------|------|------|------|---------|
| Input leakage current, high | Ішн1 | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P140, P141 | VI = EVDD0 | | | | 1 | μΑ |
| | ILIH2 | P20 to P27, P137, P150 to P154, RESET | $V_I = V_{DD}$ | | | | 1 | μΑ |
| | Ішнз | P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS) | VI = VDD | In input port or external clock input | | | 1 | μΑ |
| | | | | In resonator connection | | | 10 | μΑ |
| | ILIH4 | P20 to P27, P150 to P154 | $V_I = AV_{DD}$ | | | | 1 | μ A |
| Input leakage current, low | Iuu1 | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P67, P70 to P77, P120, P140, P141 | VI = EVsso | | | | -1 | μΑ |
| | ILIL2 | P20 to P27, P137, P150 to P154, RESET | Vı = Vss | VI = VSS | | | -1 | μА |
| | Ішз | P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS) | Vı = Vss | In input port or external clock input | | | -1 | μА |
| | | | | In resonator connection | | | -10 | μΑ |
| | ILIL4 | P20 to P27, P150 to P154 | Vı = AVss | | | | -1 | μΑ |
| On-chip pull-up resistance | R∪ | P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141 | Vi = EVsso | , In input port | 10 | 20 | 100 | kΩ |

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

Specifications in this document are tentative and subject to change.

(1/2)

| Parameter | Symbol | | | Conditions | | | MIN. | TYP. | MAX. | Unit |
|----------------|-------------|----------------|-----------------------------|--|------------------|--------------------------|------|------|------|---------|
| Supply current | IDD1 Note 1 | Operating mode | High-speed operation Note 5 | f _{IH} = 32 MHz ^{Note 3} | Basic operation | V _{DD} = 3.0 V | | 2.1 | | mA |
| | | | | | Normal operation | V _{DD} = 3.0 V | | 4.6 | 7.0 | mA |
| | | | | f _{IH} = 24 MHz ^{Note 3} | Normal operation | V _{DD} = 3.0 V | | 3.7 | 5.5 | mA |
| | | | | f _{IH} = 16 MHz ^{Note 3} | Normal operation | V _{DD} = 3.0 V | | 2.7 | 4.0 | mA |
| | | | Low-speed | fin = 8 MHz Note 3 | Normal | V _{DD} = 3.0 V | | 1.2 | 1.8 | mA |
| | | | operation Note 5 | | operation | V _{DD} = 2.0 V | | 1.2 | 1.8 | mA |
| | | | Low-voltage | fin = 4 MHz Note 3 | Nomal | V _{DD} = 3.0 V | | 1.2 | 1.7 | mA |
| | | | operation Note 5 | | operation | V _{DD} = 2.0 V | | 1.2 | 1.7 | mA |
| | | | High-speed | $f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ | Nomal | Square wave input | | 3.0 | 4.6 | mA |
| | | | operation Note 5 | $V_{DD} = 3.0 \text{ V}$ | operation | Resonator connection | | 3.2 | 4.8 | mA |
| | | | | $f_{MX} = 10 \text{ MHz}^{Note 2},$ | Normal | Square wave input | | 1.9 | 2.7 | mA |
| | | | | $V_{DD} = 3.0 \text{ V}$ | operation | Resonator connection | | 1.9 | 2.7 | mA |
| | | | Low-speed | $f_{MX} = 8 MHz^{Note 2}$ | Normal | Square wave input | | 1.1 | 1.7 | mA |
| | | | operation Note 5 | $V_{DD} = 3.0 \text{ V}$ | operation | Resonator connection | | 1.1 | 1.7 | mA |
| | | | | $f_{MX} = 8 MHz^{Note 2}$ | Normal | Square wave input | | 1.1 | 1.7 | mA |
| | | | | $V_{DD} = 2.0 \text{ V}$ | operation | Resonator connection | | 1.1 | 1.7 | mA |
| | | | Subsystem | fsuB = 32.768 kHz | Nomal | Square wave input | | 4.1 | | μA |
| | | | clock operation | Note 4 $T_A = -40^{\circ}C$ | operation | Resonator connection | | 4.2 | | μΑ |
| | | | | fsub = 32.768 kHz | Nomal | Square wave input | | 4.1 | 4.9 | μA |
| | | | | T _A = +25°C | operation | Resonator connection | | 4.2 | 5.0 | μΑ |
| | | | | fsub = 32.768 kHz | Normal | Square wave input | | 4.2 | 5.5 | μ A |
| | | | | Note 4 $T_A = +50^{\circ}C$ | operation | Resonator connection | | 4.3 | 5.6 | μΑ |
| | | | | fsub = 32.768 kHz | Normal | Square wave input | | 4.2 | 6.3 | μA |
| | | | | Note 4 | operation | Resonator connection | | 4.2 | 6.4 | μA |
| | | | | T _A = +70°C | | 1 ISSUITATION CONTINUOUS | | 7.0 | 0.4 | μη |
| | | | | fsub = 32.768 kHz | Normal | Square wave input | | 4.8 | 7.7 | μΑ |
| | | | | Note 4 | operation | Resonator connection | | 4.9 | 7.8 | μΑ |
| | | | | T _A = +85°C | | | | | | |

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current (except for background operation (BGO)). However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When real-time counter and watchdog timer is stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

High speed operation: VDD = 2.7 V to 3.6 V@1 MHz to 32 MHz, VDD = 2.4 V to 3.6 V@1 MHz to 16 MHz

Low speed operation: VDD = 1.8 V to 3.6 V@1 MHz to 8 MHz Low voltage operation: VDD = 1.6 V to 3.6 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to $+85^{\circ}$ C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

(2/2)

| Parameter | Symbol | | | Conditions | | MIN. | TYP. | MAX. | Unit |
|-----------|------------------------|------------------------|------------------------|--|-------------------------|------|------|------|------|
| Supply | I _{DD2} | HALT | High-speed | f _{IH} = 32 MHz ^{Note 4} | V _{DD} = 3.0 V | | 0.54 | 1.63 | mA |
| current | Note 2 | mode | operation Note 7 | f _{IH} = 24 MHz ^{Note 4} | V _{DD} = 3.0 V | | 0.44 | 1.28 | mA |
| | | | | fih = 16 MHz Note 4 | V _{DD} = 3.0 V | | 0.40 | 1.00 | mA |
| | | | Low-speed | fih = 8 MHz Note 4 | V _{DD} = 3.0 V | | 260 | 530 | μА |
| | | | operation Note 7 | | V _{DD} = 2.0 V | | 260 | 530 | μА |
| | | | Low-voltage | f _{IH} = 4 MHz ^{Note 4} | V _{DD} = 3.0 V | | 420 | 640 | μА |
| | | | operation Note 7 | | V _{DD} = 2.0 V | | 420 | 640 | μА |
| | | | High-speed | $f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ | Square wave input | | 0.28 | 1.00 | mA |
| | | | operation Note 7 | $V_{DD} = 3.0 \text{ V}$ | Resonator connection | | 0.45 | 1.17 | mA |
| | | | | $f_{MX} = 10 \text{ MHz}^{Note 3},$ | Square wave input | | 0.19 | 0.60 | mA |
| | | | | $V_{DD} = 3.0 \text{ V}$ | Resonator connection | | 0.26 | 0.67 | mA |
| | | | Low-speed | $f_{MX} = 8 MHz^{Note 3}$ | Square wave input | | 95 | 330 | μΑ |
| | | | operation Note 7 | $V_{DD} = 3.0 \text{ V}$ | Resonator connection | | 145 | 380 | μΑ |
| | | | | $f_{MX} = 8 MHz^{Note 3}$ | Square wave input | | 95 | 330 | μA |
| | | | | V _{DD} = 2.0 V | Resonator connection | | 145 | 380 | μА |
| | | | Subsystem | fsub = 32.768 kHz ^{Note 5} | Square wave input | | 0.25 | | μA |
| | | | clock operation | T _A = -40°C | Resonator connection | | 0.44 | | μА |
| | | | орегация | $f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$ | Square wave input | | 0.30 | 0.57 | μΑ |
| | | | | T _A = +25°C | Resonator connection | | 0.49 | 0.76 | μΑ |
| | | | | fsub = 32.768 kHz ^{Note 5} | Square wave input | | 0.33 | 1.17 | μΑ |
| | | | | T _A = +50°C | Resonator connection | | 0.52 | 1.36 | μΑ |
| | | | | fsub = 32.768 kHz ^{Note 5} | Square wave input | | 0.36 | 1.97 | μΑ |
| | | | | T _A = +70°C | Resonator connection | | 0.55 | 2.16 | μΑ |
| | | | | fsuв = 32.768 kHz ^{Note 5} | Square wave input | | 0.97 | 3.37 | μA |
| | | | | T _A = +85°C | Resonator connection | | 1.16 | 3.56 | μA |
| | IDD3 ^{Note 6} | STOP | T _A = -40°C | | | | 0.18 | | μA |
| | | T _A = +25°C | | | | 0.23 | 0.50 | μA | |
| | | | T _A = +50°C | | | 0.26 | 1.10 | μA | |
| | | | T _A = +70°C | | | | 0.29 | 1.90 | μΑ |
| | | | T _A = +85°C | | | | 0.90 | 3.30 | μA |

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When operating real-time clock (RTC) and setting ultra-low current consumption (AMPHS1 = 1). When high-speed on-chip oscillator and high-speed system clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.
 - 6. When high-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as

High speed operation: VDD = 2.7 V to 3.6 V@1 MHz to 32 MHz, VDD = 2.4 V to 3.6 V@1 MHz to 16 MHz

Low speed operation: VDD = 1.8 V to 3.6 V@1 MHz to 8 MHz Low voltage operation: VDD = 1.6 V to 3.6 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fIH: High-speed on-chip oscillator clock frequency
 - 3. fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | | Conditions | 3 | MIN. | TYP. | MAX. | Unit |
|--------------------------------------|-----------------|---|-------------------|----------------------------------|------|------|-------|------|
| RTC operating | IRTC Notes 1, 2 | fsuB = 32.768 kHz | Real-time clock | operation | | 0.02 | | μА |
| current | | | Interval timer op | Interval timer operation | | | | |
| Watchdog timer operating current | WDT Notes 2, 3 | fı∟ = 15 kHz | | | | 0.22 | | μΑ |
| A/D converter | IADC Note 4 | Reference power | | | | 460 | 1090 | μА |
| operating current | | than the internal re $AV_{DD} = 3.6 \text{ V}$ | eference voltage, | ANI16 to ANI30 | | 400 | 950 | μΑ |
| | | Reference power s internal reference v AVDD = 3.6 V | | ANI0 to ANI12, ANI16 to ANI30 | | 400 | 950 | μΑ |
| Temperature sensor operating current | Ітмрѕ | | | | | 75 | | μΑ |
| LVD operating current | ILVI Note 5 | | | | | 0.08 | | μА |
| BGO operating current | IBGO Note 6 | | | | | 2.50 | 12.20 | mA |

- Notes 1. Current flowing only to the real-time clock (excluding the operating current of the XT1 oscillator). The TYP. value of the current value of the RL78/G1A is the sum of the TYP. values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. The IDD1 and IDD2 MAX. values also include the real-time clock operating current. However, IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78/G1A is the sum of IDD1, IDD2 or IDD3 and IWDT when fCLK = fSUB when the watchdog timer operates in STOP mode.
 - 4. Current flowing only to the A/D converter. The current value of the RL78/G1A is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 5. Current flowing only to the LVD circuit. The current value of the RL78/G1A is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
 - 6. Current flowing only to the BGO. The current value of the RL78/G1A is the sum of IDD1 or IDD2 and IBG0 when the BGO operates in an operation mode.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is TA = 25°C

2.4 AC Characteristics

2.4.1 Basic operation

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{AV} \text{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{EV} \text{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV} \text{sso} = 0 \text{ V})$

| Items | Symbol | | Con | ditions | | MIN. | TYP. | MAX. | Unit |
|--|---|----------------------------------|------------------|---------|---|-----------|------|------|--------------------|
| Instruction cycle (minimum | Тсч | Main | High-s | | $2.7 V \le V_{DD} \le 3.6 V$ | 0.03125 | | 1 | μS |
| instruction execution time) | | system | main n | node | $2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$ | 0.0625 | | 1 | μS |
| | | clock (fmain) operation | Low vo | • | $1.6 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ | 0.25 | | 1 | μS |
| | | | Low-sp main n | | $1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ | 0.125 | | 1 | μS |
| | | Subsystem coperation | lock (fs | ив) | $1.8 V \leq V_{DD} \leq 3.6 V$ | 28.5 | 30.5 | 31.3 | μS |
| | | In the self | High-s | peed | $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ | 0.03125 | | 1 | μS |
| | | programming | main n | node | $2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$ | 0.0625 | | 1 | μS |
| | | mode | Low vo | | $1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ | 0.25 | | 1 | μS |
| | | | Low-sp | • | $1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ | 0.125 | | 1 | μS |
| External main system clock | fex | 2.7 V ≤ V _{DD} ≤ | 3.6 V | | | 1.0 | | 20.0 | MHz |
| frequency | | 1.8 V ≤ V _{DD} < | < 2.7 V | | | 1.0 | | 8.0 | MHz |
| | | 1.6 V ≤ V _{DD} < | < 1.8 V | | | 1.0 | | 4.0 | MHz |
| | fexs | | | | | 32 | | 35 | kHz |
| External main system clock input | texh, texl | $2.7 \text{ V} \leq V_{DD} \leq$ | ≤ 3.6 V | | | 24 | | | ns |
| high-level width, low-level width | | $1.8~V \le V_{DD} < 2.7~V$ | | 60 | | | ns | | |
| | $1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V}$ | | | 120 | | | ns | | |
| | texhs, texhs | | | | | 13.7 | | | μS |
| TI00, TI01, TI03 to TI07 input high-level width, low-level width | tтін, tтіL | | | | | 1/fмск+10 | | | ns ^{Note} |
| TO00, TO01, TO03 to TO07 | fто | High-speed r | main 2 | 2.7 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 8 | MHz |
| output frequency | | mode | | 1.8 V ≤ | ≤ EV _{DD0} < 2.7 V | | | 4 | MHz |
| | | | - | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V | | | 2 | MHz |
| | | Low voltage main mode | | 1.6 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 2 | MHz |
| | | Low-speed m | nain ' | 1.8 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 4 | MHz |
| | | mode | | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V | | | 2 | MHz |
| PCLBUZ0, PCLBUZ1 output | fpcL | High-speed r | main 2 | 2.7 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 8 | MHz |
| frequency | | mode | - | 1.8 V ≤ | ≤ EV _{DD0} < 2.7 V | | | 4 | MHz |
| | | | | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V | | | 2 | MHz |
| | | Low voltage | main · | 1.8 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 4 | MHz |
| | | mode | - | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V | | | 2 | MHz |
| | | Low-speed m | nain | 1.8 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | | | 4 | MHz |
| | | mode | - | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V | | | 2 | MHz |
| Interrupt input high-level width, | tinth, | INTP0 | | 1.6 V ≤ | ≤ V _{DD} ≤ 3.6 V | 1 | | | μS |
| low-level width | t INTL | INTP1 to INT | P11 | 1.6 V ≤ | ≤ EV _{DD0} ≤ 3.6 V | 1 | | | μS |
| Key interrupt input low-level width | tkr | KR0 to KR9 | - | 1.8 V ≤ | ≤ EV _{DD0} ≤ 3.6 V, | 250 | | | ns |
| | | | - | 1.8 V ≤ | $\leq AV_{DD} \leq 3.6 V$ | | | | |
| | | | - | 1.6 V ≤ | ≤ EV _{DD0} < 1.8 V, | 1 | | | μS |
| | | | - | 1.6 V ≤ | ≤ AV _{DD} < 1.8 V | | | | |
| RESET low-level width | trsl | | l l | | | 10 | | | μS |

(Note, Caution and Remark are listed on the next page.)



Note The following conditions are required for low voltage interface when EVDDO < VDD

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MIN. } 250 \text{ ns}$

Caution Always use AVDD pin with the same potential as the VDD pin.

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



2.5 Peripheral Functions Characteristics

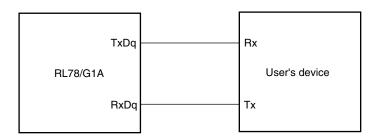
2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (dedicated baud rate generator output)

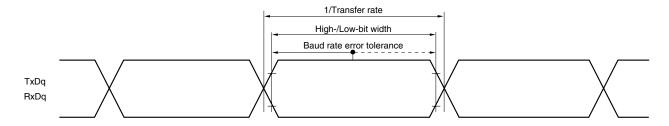
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|----------------------|--------|---|------|------|---------------|------|
| Transfer rate Note 1 | | | | | fmck/6 Note 2 | bps |
| | | Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk | | | 5.3 | Mbps |

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- Notes 1. Transfer rate in the SNOOZE mode is max. 9600 bps, min. 4800 bps.
 - 2. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}: \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V}: \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}: \text{MAX. } 0.6 \text{ Mbps}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode (fmck/2), SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|--|--|--------------|------|------|------|
| SCKp cycle time | tkcy1 | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | 83.3 Note 1 | | | ns |
| SCKp high-/low-level width | t _{KH1} , t _{KL1} | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | tkcy1/2 - 10 | | | ns |
| SIp setup time (to SCKp↑) Note 2 | tsıĸ1 | $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V}$ | 33 Note 5 | | | ns |
| SIp hold time (from SCKp↑) Note 3 | t _{KSI1} | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | 10 | | | ns |
| Delay time from SCKp↓ to SOp output Note 4 | tkso1 | C = 20 pF ^{Note 6} | | | 10 | ns |

- Notes 1. The value must also be 2/fclk or more.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 5. Using the fmck within 24 MHz.
 - 6. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - **2.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode (fmck/4), SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|------------------|-----------------------------------|------------------|------|------|------|
| SCKp cycle time | tkcy1 | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | 125 Note 1 | | | ns |
| | | $2.4~V \leq EV_{DD0} \leq 3.6~V$ | 250 Note 1 | | | ns |
| | | 1.8 V ≤ EV _{DD0} ≤ 3.6 V | 500 Note 1 | | | ns |
| | | 1.6 V ≤ EV _{DD0} ≤ 3.6 V | 1000 Note 1 | | | ns |
| SCKp high-/low-level width | tкн1, | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | tkcy1/2 - 18 | | | ns |
| | t _{KL1} | $2.4~V \leq EV_{DD0} \leq 3.6~V$ | tkcy1/2 - 38 | | | ns |
| | | 1.8 V ≤ EV _{DD0} ≤ 3.6 V | tkcy1/2 - 50 | | | ns |
| | | 1.6 V ≤ EV _{DD0} ≤ 3.6 V | tксу1/2 — 100 | | | ns |
| SIp setup time (to SCKp↑) Note 2 | tsıĸ1 | $2.7~V \leq EV_{DD0} \leq 3.6~V$ | 38 | | | ns |
| | | $2.4~V \leq EV_{DD0} \leq 3.6~V$ | 75 | | | ns |
| | | 1.8 V ≤ EV _{DD0} ≤ 3.6 V | 150 | | | ns |
| | | 1.6 V ≤ EV _{DD0} ≤ 3.6 V | 300 | | | ns |
| SIp hold time (from SCKp↑) Note 3 | tksi1 | | 19 | | | ns |
| Delay time from SCKp↓ to SOp output Note 4 | tkso1 | C = 30 pF ^{Note 5} | | | 25 | ns |

- Notes 1. The value must also be 4/fclk or more.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from $\overline{SCKp}\uparrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **5.** C is the load capacitance of the \overline{SCKp} and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - 2. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 2), g: PIM and POM numbers (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(4) During communication at same potential (CSI mode) (slave mode, \overline{SCKp} ... external clock input) (T_A = -40 to +85°C, 1.6 V \leq EV_{DD0} \leq V_{DD} \leq 3.6 V, Vss = EV_{SS0} = 0 V)

| Parameter | Symbol | Cond | litions | MIN. | TYP. | MAX. | Unit |
|----------------------------|-------------------|--|-----------------------------------|-----------|------------|------------|------|
| SCKp cycle time Note 5 | tkcy2 | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}$ | 16 MHz < fмск | 8/fмск | | | ns |
| | | | fмcк ≤ 16 MHz | 6/fмск | | | ns |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$ | 16 MHz < fмск | 8/fмск | | | ns |
| | | | fмcк ≤ 16 MHz | 6/fмск | | | ns |
| | | 1.6 V ≤ EV _{DD0} < 1.8 V | V | 6/fмск | | | ns |
| SCKp high-/low-level width | tкн2, tкL2 | 1.6 V ≤ EVDD0≤ 3.6 V | | tксү2/2 | | | ns |
| SIp setup time | tsık2 | $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V}$ | J | 50 | | | ns |
| (to SCKp↑) Note 1 | | 1.8 V ≤ EV _{DD0} < 2.7 V | | 80 | | | ns |
| | | 1.6 V ≤ EV _{DD0} < 1.8 V | V | 160 | | | ns |
| Slp hold time | t _{KSI2} | $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V}$ | / | 1/fмск+31 | | | ns |
| (from SCKp↑) Note 2 | | 1.8 V ≤ EV _{DD0} < 2.7 V | V | 1/fмск+31 | | | ns |
| | | 1.6 V ≤ EV _{DD0} < 1.8 V | 1.6 V ≤ EV _{DD0} < 1.8 V | | | | ns |
| Delay time from SCKp↓ to | tkso2 | C = 30 pF Note 4 | $2.7~V \le EV_{DD0} < 3.6~V$ | | | 2/fмск+44 | ns |
| SOp output Note 3 | | | 2.4 V ≤ EV _{DD0} < 2.7 V | | | 2/fмск+75 | ns |
| | | 1.8 V ≤ EV _{DD0} < 2.4 V | | | 2/fмск+110 | ns | |
| | | | 1.6 V ≤ EV _{DD0} < 1.8 V | | | 2/fmck+220 | ns |

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $\frac{1}{SCKp}$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from $\overline{SCKp}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from $\overline{SCKp}\uparrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 2),

g: PIM number (g = 0, 1)

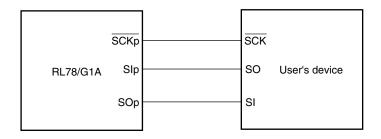
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). $\,$ m: Unit number,

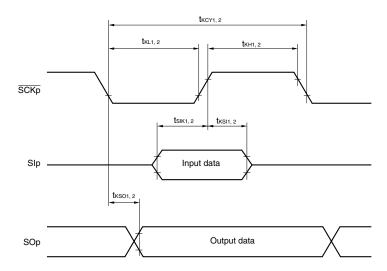
n: Channel number (mn = 00 to 03, 10, 11))

Specifications in this document are tentative and subject to change.

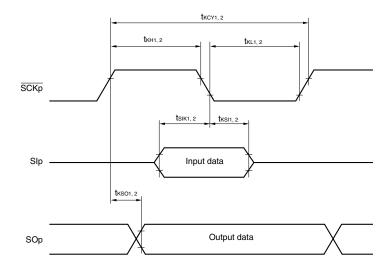
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

(5) During communication at same potential (simplified I²C mode)

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

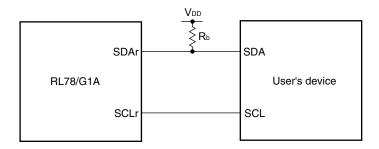
| Parameter | Symbol | Conditions | MIN. | MAX. | Unit |
|-------------------------------|---------------|---|--------------|------|------|
| SCLr clock frequency | fscL | $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$ | | 1000 | kHz |
| | | $C_b = 50$ pF, $R_b = 2.7$ k Ω | | | |
| | | $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$ | | 400 | kHz |
| | | $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ | | 300 | kHz |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ | | 250 | kHz |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| Hold time when SCLr = "L" | tLOW | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ | 475 | | ns |
| | | $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | |
| | | $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$ | 1150 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ | 1550 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ | 1850 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| Hold time when SCLr = "H" | t HIGH | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ | 475 | | ns |
| | | $C_b = 50$ pF, $R_b = 2.7$ k Ω | | | |
| | | $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6 \text{ V},$ | 1150 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ | 1550 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ | 1850 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| Data setup time (reception) | tsu:dat | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ | 1/fмск + 85 | | ns |
| | | $C_b = 50$ pF, $R_b = 2.7$ k Ω | Note | | |
| | | $1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 3.6 \text{ V},$ | 1/fmck + 145 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$ | Note | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ | 1/fmck + 230 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | Note | | |
| | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ | 1/fmck + 290 | | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | Note | | |
| Data hold time (transmission) | thd:dat | $2.7~V \leq EV_{DD0} \leq 3.6~V,$ | 0 | 305 | ns |
| | | $C_b = 50$ pF, $R_b = 2.7$ k Ω | | | |
| | | $1.8~V \leq EV_{DD0} \leq 3.6~V,$ | 0 | 355 | ns |
| | | $C_b = 100 \ pF, \ R_b = 3 \ k\Omega$ | | | |
| | | $1.8~V \leq EV_{DD0} < 2.7~V,$ | 0 | 405 | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |
| | | $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ | 0 | 405 | ns |
| | | $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$ | | | |

Note Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

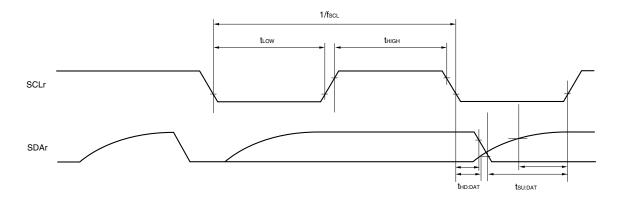
(Caution and Remarks are listed on the next page.)

Specifications in this document are tentative and subject to change.

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

- Remarks 1. $R_b[\Omega]$:Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance
 - 2. r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1), h: POM number (h = 0, 1)
 - fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number
 (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)

2. ELECTRICAL SPECIFICATIONS

Caution The pins mounted depend on the product. Refer to 1.3.1 25-pin products to 1.3.4 64-pin products.

(6) Communication at different potential (2.5 V) (UART mode) (dedicated baud rate generator output) (1/2) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} < \text{EV}_{DD0} < \text{V}_{DD} < 3.6 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

| (IA = - 1 0 t | (1A = -40 to +65 C, 1.8 V \(\) \(\ | | | | | | | | | |
|--------------------------|--|-----------|--|---|--|------|--------------------------|------|--|--|
| Parameter | Symbol | | Conditions | | | TYP. | MAX. | Unit | | |
| Transfer rate | | reception | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$ | | | | fmck/6 ^{Note 1} | bps | | |
| | | | $2.3~V \leq V_b \leq 2.7~V$ | Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk | | | 5.3 | Mbps | | |
| | | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$ | | | | fMCK/6 Notes 1 to 3 | bps | | |
| | | | | Theoretical value of the maximum transfer rate fclk = 8 MHz, fMck = fclk | | | 1.3 | Mbps | | |

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 9600 bps, MIN. 4800 bps
 - 2. Use it with EVDD0≥Vb.
 - 3. The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$: MAX. 2.6 Mbps $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MAX. } 0.6 \text{ Mbps}$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. V_b[V]: Communication line voltage
 - 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

- n: Channel number (mn = 00 to 03, 10, 11)
- 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

$$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$$
: VIH = $2.0 \text{ V}, \ \text{VIL} = 0.5 \text{ V}$

$$1.8~V \le EV_{DD0} < 3.3~V,~1.6~V \le V_b \le 2.0~V;~V_{IH} = 1.5~V,~V_{IL} = 0.32~V$$

5. UART2 cannnot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (2.5 V) (UART mode) (dedicated baud rate generator output) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | | Conditions | | | | MAX. | Unit |
|---------------|--------|--------------|--|--|--|--|------------------|------|
| Transfer rate | | transmission | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$ | | | | Notes | bps |
| | | | $2.3~V \leq V_b \leq 2.7~V$ | Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$ | | | 1.2 Note 5 | Mbps |
| | | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$ | | | | Notes 1, 4, 5 | bps |
| | | | | Theoretical value of the maximum transfer rate | | | 0.43 Note 6 | Mbps |
| | | | | $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$ | | | | |

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 9600 bps, MIN. 4800 bps
 - 2. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 3.6 V and 2.3 V \leq V_b \leq 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{ \{ -C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b}) \} \times 3 }$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 3. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 2 above to calculate the maximum transfer rate under conditions of the customer.
- 4. Use it with EVDD0 ≥ Vb.
- 5. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 6. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 7 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

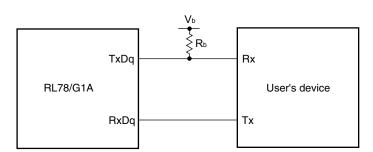
- **Remarks 1.** $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 - **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

$$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} : \text{V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V}$$

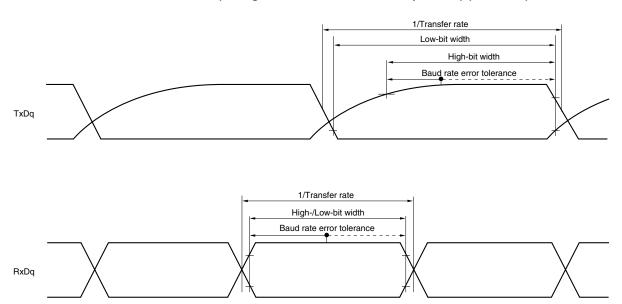
$$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} : \text{V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V}$$

5. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** UART2 cannot communicate at different potentia when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.
 - 2. $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage
 - 3. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

(7) Communication at different potential (2.5 V) (fMck/2) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

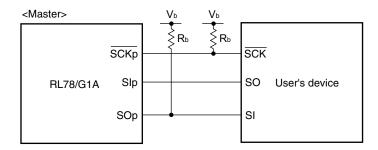
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--------------------------|------------------|---|--------------|------|------|------|
| SCKp cycle time | tkcy1 | $2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$ | 300 Note 1 | | | ns |
| | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| SCKp high-level width | t _{KH1} | $2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$ | tkcy1/2 - | | | ns |
| | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | 120 | | | |
| SCKp low-level width | t _{KL1} | $\label{eq:2.7} 2.7~V \leq EV_{\text{DD0}} < 3.6~V, 2.3~V \leq V_{\text{b}} \leq 2.7~V,$ | tkcy1/2 - 10 | | | ns |
| | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Slp_setup time | tsıĸı | $2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | 121 | | | ns |
| (to SCKp↑) Note 2 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Slp hold time | tksi1 | $\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \\ \end{array}$ | 10 | | | ns |
| (from SCKp↑) Note 2 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Delay time from SCKp↓ to | tkso1 | $\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$ | | | 130 | ns |
| SOp output Note 2 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Slp_setup time | tsıĸ1 | $\label{eq:2.7} \begin{array}{c} 2.7 \ V \leq EV_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \end{array}$ | 33 | | | ns |
| (to SCKp↓) Note 3 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Slp hold time | tksi1 | $\label{eq:2.7} \begin{array}{c} 2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$ | 10 | | | ns |
| (from SCKp↓) Note 3 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| Delay time from SCKp↑ to | tkso1 | $\label{eq:2.7} \begin{array}{c} 2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \end{array}$ | | | 10 | ns |
| SOp output Note 3 | | $C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |

Notes 1. The value must also be 2/fclk or more.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 3. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remark are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** Rb[Ω]:Communication line (\overline{SCKp} , SOp) pull-up resistance, Cb[F]: Communication line (\overline{SCKp} , SOp) load capacitance, Vb[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$$
: Vih = $2.0 \text{ V}, \ \text{Vil} = 0.5 \text{ V}$

4. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)

(8) Communication at different potential (2.5 V) (fmck/4) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C. } 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V. V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-----------------------|------------------|---|--------------|------|------|------|
| SCKp cycle time | tkcy1 | $2.7~V \leq EV_{DD0} < 3.6~V, 2.3~V \leq V_b \leq 2.7~V,$ | 500 Note | | | ns |
| | | $C_b = 30$ pF, $R_b = 2.7$ k Ω | | | | |
| | | $1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ | 1150 Note | | | ns |
| | | $C_b = 30$ pF, $R_b = 5.5$ k Ω | | | | |
| SCKp high-level width | tкн1 | $2.7 \ V \leq \text{EV}_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | tксү1/2 — | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | 170 | | | |
| | | $1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ | tkcy1/2 - | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | 458 | | | |
| SCKp low-level width | t _{KL1} | $2.7 \ V \leq \text{EV}_{\text{DD0}} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | tkcy1/2 - 18 | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $\label{eq:loss_loss} \begin{array}{ l c c c c c c c c c c c c c c c c c c $ | tkcy1/2 - 50 | | | ns |
| | | $C_b = 30$ pF, $R_b = 5.5$ k Ω | | | | |

Note The value must also be 4/fclk or more.

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
 - 2. Use it with EVDD0 ≥ Vb.
- **Remarks 1.** $R_b[\Omega]$: Communication line (\overline{SCKp} , SOp) pull-up resistance, $C_b[F]$: Communication line (\overline{SCKp} , SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} : \text{V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V}$$

$$1.8 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} : \text{V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V}$$

4. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2. ELECTRICAL SPECIFICATIONS

Caution The pins mounted depend on the product. Refer to 1.3.1 25-pin products to 1.3.4 64-pin products.

(8) Communication at different potential (2.5 V) (fmck/4) (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

Specifications in this document are tentative and subject to change.

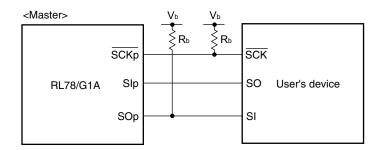
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|-------------------|--|------|------|------|------|
| SIp setup time | tsıĸ1 | $2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | 177 | | | ns |
| (to SCKp↑) Note 1 | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ | 479 | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |
| Slp hold time | t _{KSI1} | $2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | 19 | | | ns |
| (from SCKp↑) Note 1 | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ | 19 | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |
| Delay time from SCKp↓ to | tkso1 | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ | | | 195 | ns |
| SOp output Note 1 | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ | | | 483 | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |
| SIp setup time | tsıĸ1 | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ | 44 | | | ns |
| (to SCKp↓) Note 2 | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \ V \le EV_{DD0} < 3.3 \ V, \ 1.6 \ V \le V_b \le 2.0 \ V,$ | 110 | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |
| Slp hold time | tksi1 | $2.7 \ V \leq EV_{DD0} < 3.6 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$ | 19 | | | ns |
| $(from \overline{SCKp}_{\downarrow})^{Note 2}$ | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ | 19 | | | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |
| Delay time from SCKp↑ to | tkso1 | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ | | | 25 | ns |
| SOp output Note 2 | | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | | |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ | | | 25 | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ | | | | |

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Cautions and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

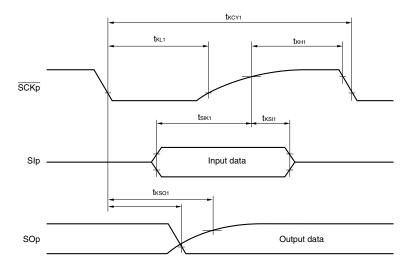


- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
 - 2. Use it with EVDD0 ≥ Vb.
- **Remarks 1.** R_b[Ω]:Communication line (\overline{SCKp} , SOp) pull-up resistance, C_b[F]: Communication line (\overline{SCKp} , SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

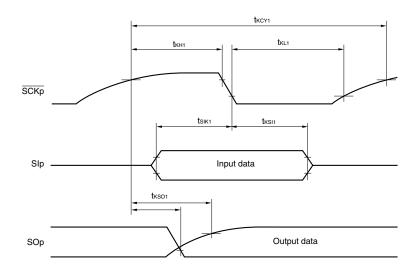
$$\begin{split} 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \text{: V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V} \\ 1.8 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{: V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V} \end{split}$$

4. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (m = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)

2. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (2.5 V) (CSI mode) (slave mode, SCKp... external clock input) (Ta = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

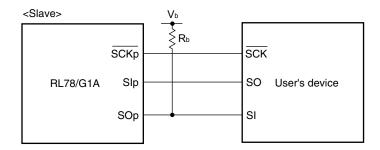
| Parameter | Symbol | C | Conditions | MIN. | TYP. | MAX. | Unit |
|--------------------------------------|---------------|---|--|-----------------|------|----------|------|
| SCKp cycle time Note 1 | tkcy2 | $2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 3.6 \text{ V},$ | 24 MHz < fмск | 20/fмск | | | ns |
| | | $2.3 \ V \le V_b \le 2.7 \ V$ | 20 MHz < fмcк≤ 24 MHz | 16/ fмск | | | ns |
| | | | 16 MHz < fмcк≤ 20 MHz | 14/fмск | | | ns |
| | | | 8 MHz < fмcк≤ 16 MHz | 12/fмск | | | ns |
| | | | 4 MHz < fмcк≤8 MHz | 8/fмск | | | ns |
| | | | fмcк≤ 4 MHz | 6/fмск | | | ns |
| | | $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ | 24 MHz < fмск | 48/f мск | | | ns |
| | | $1.6~V \le V_b \le 2.0~V^{\text{Note 2}}$ | 20 MHz < fмcк≤ 24 MHz | 36/fмск | | | ns |
| | | | 16 MHz < fмcк≤ 20 MHz | 32/fмск | | | ns |
| | | | 8 MHz < fмcк≤ 16 MHz | 26/fмск | | | ns |
| | | | 4 MHz < fмcк≤8 MHz | 16/f мск | | | ns |
| | | | fмcк ≤ 4 MHz | 10/fмск | | | ns |
| SCKp high-/low-level width | tкн2, tкL2 | 2.7 V ≤ EV _{DD0} < 3.6 | S V, 2.3 V \leq V _b \leq 2.7 V | tkcy2/2 - 18 | | | ns |
| | | 1.8 V ≤ EV _{DD0} < 3.3 | tkcy2/2 - 50 | | | ns | |
| SIp setup time | tsık2 | 2.7 V ≤ EV _{DD0} ≤ 3.6 | S V | 60 | | | ns |
| (to SCKp↑) Note 3 | | 1.8 V ≤ EV _{DD0} < 3.3 | 3 V | 97 | | | ns |
| SIp hold time (from SCKp↑) Note 4 | tksi2 | | | 1/fмck + 31 | | | ns |
| Delay time from SCKp↓ to | tkso2 | 2.7 V ≤ EV _{DD0} < 3.6 | $6 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ | | | 2/fмск + | ns |
| SOp output Note 5 | | C _b = 30 pF, R _b = 2. | $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ | | | 214 | |
| | | $1.8 \ V \leq EV_{DD0} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}},$ | | | | 2/fмск + | ns |
| | | $C_b = 30 \text{ pF}, R_b = 5.$ | 5 kΩ | | | 573 | |

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $\overline{\text{SCKp}}\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp1" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

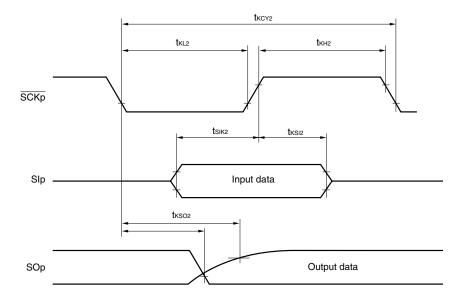
- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
 - **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

$$\begin{split} 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.6 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \text{: V}_{\text{IH}} = 2.0 \text{ V}, \ \text{V}_{\text{IL}} = 0.5 \text{ V} \\ 1.8 \text{ V} &\leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{: V}_{\text{IH}} = 1.5 \text{ V}, \ \text{V}_{\text{IL}} = 0.32 \text{ V} \end{split}$$

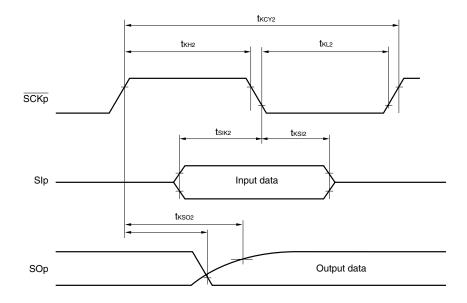
5. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Specifications in this document are tentative and subject to change.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number, n: Channel number (mn = 00, 01, 02, 10), g: PIM and POM number (g = 0, 1)

2. CSI01, CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (2.5 V) (simplified I²C mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | MAX. | Unit |
|---------------------------|--------|---|------|------|------|
| SCLr clock frequency | fscL | $\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$ | | 1000 | kHz |
| | | $\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$ | | 400 | kHz |
| | | $\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$ | | 300 | kHz |
| Hold time when SCLr = "L" | tLOW | $\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$ | 475 | | ns |
| | | $\begin{split} & 2.7 \; V \leq EV_{DD0} \leq 3.6 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$ | 1150 | | ns |
| | | $\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$ | 1550 | | ns |
| Hold time when SCLr = "H" | tнівн | $\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$ | 200 | | ns |
| | | $\begin{split} & 2.7 \; V \leq EV_{DD0} \leq 3.6 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$ | 600 | | ns |
| | | $\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{Note \; 1}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$ | 610 | | ns |

(Notes, Caution and Remarks are listed on the next page.)

(10) Communication at different potential (2.5 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | MAX. | Unit |
|-------------------------------|---------|--|------------------------------------|------|------|
| Data setup time (reception) | tsu:dat | $\begin{split} 2.7 \ V &\leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$ | 1/f _{MCK} + 135 Note 2 | | ns |
| | | $\label{eq:substitute} \begin{array}{ c c c } \hline 2.7 \ V \leq EV_{DD0} \leq 3.6 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$ | 1/f _{MCK} + 190 Note 2 | | ns |
| | | $ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Notes 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $ | 1/fMCK + 190 Note 2 | | ns |
| Data hold time (transmission) | thd:dat | $ \begin{aligned} 2.7 & V \leq EV_{DD0} \leq 3.6 & V, \\ 2.3 & V \leq V_b \leq 2.7 & V, \\ C_b = 50 & pF, & R_b = 2.7 & k\Omega \end{aligned} $ | 0 | 305 | ns |
| | | $\label{eq:substitute} \begin{split} & 2.7 \; V \leq EV_{DD0} \leq 3.6 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$ | 0 | 355 | ns |
| | | $ \begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 1}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $ | 0 | 405 | ns |

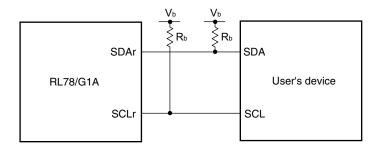
Notes 1. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

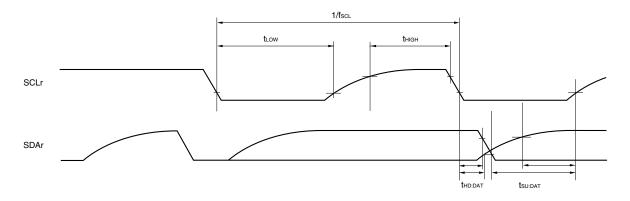
(Remarks is listed on the next page.)

^{2.} Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20), g: PIM, POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00, 01, 02, 10)
 - **4.** V_{IH} and V_{IL} below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in simplified I²C mode mode.

$$2.7~V \leq EV_{DD0} < 3.6~V,~2.3~V \leq V_b \leq 2.7~V;~V_{IH} = 2.0~V,~V_{IL} = 0.5~V$$

$$1.8~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V;~V_{IH} = 1.5~V,~V_{IL} = 0.32~V$$

Serial interface IICA 2.5.2

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

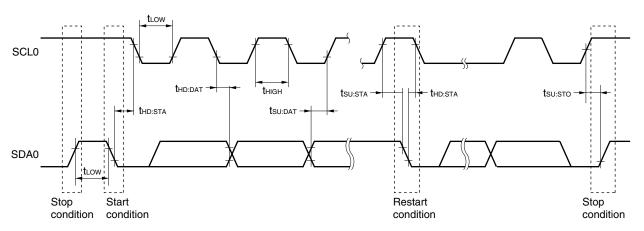
| Parameter | Symbol | Conditions | | hbol Conditions Standard Mode | | | | | | Fast Mode Plus | | Unit |
|---|--------------|---------------------------------|--------------------------------|-------------------------------|------|------|------|------|------|-------------------|--|------|
| | | | | MIN. | MAX. | MIN. | MAX. | MIN. | MAX. | | | |
| SCLA0 clock frequency | fscL | Fast mode plus: fclk≥ 10 MHz | $2.7~V \le EV_{DD0} \le 3.6~V$ | | | | | 0 | 1000 | kHz | | |
| | | Fast mode: fclk≥ 3.5 MHz | $1.8~V \le EV_{DD0} \le 3.6~V$ | | | 0 | 400 | | | kHz | | |
| | | Normal mode: fclk≥ 1 MHz | $1.6~V \le EV_{DD0} \le 3.6~V$ | 0 | 100 | | | | | kHz | | |
| Setup time of restart condition | tsu:sta | | | 4.7 | | 0.6 | | 0.26 | | μS | | |
| Hold time ^{Note 1} | thd:STA | | | 4.0 | | 0.6 | | 0.26 | | μS | | |
| Hold time when SCLA0 = "L" | tLOW | | | 4.7 | | 1.3 | | 0.5 | | μS | | |
| Hold time when SCLA0 = "H" | tніgн | | | 4.0 | | 0.6 | | 0.26 | | μS | | |
| Data setup time (reception) | tsu:dat | | | 250 | | 100 | | 50 | | ns | | |
| Data hold time (transmission) ^{Note 2} | thd:dat | | | 0 | 3.45 | 0 | 0.9 | 0 | | μS | | |
| Setup time of stop condition | tsu:sto | | | 4.0 | | 0.6 | | 0.26 | | μS | | |
| Bus-free time | t BUF | | | 4.7 | | 1.3 | | 0.5 | | μS | | |

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of tho:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b=320$ pF, $R_b=1.1~k\Omega$ Fast mode plus: $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



2.5.3 On-chip debug (UART)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|---------------|--------|------------|---------|------|------|------|
| Transfer rate | | | 115.2 k | | 1 M | bps |

Specifications in this document are tentative and subject to change.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

(1) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI0 to ANI12 (supply ANI pin to AVDD)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, 1.6 \text{ V} \le \text{AV}_{DD} \le 3.6 \text{ V}, \text{Vss} = 0 \text{ V}, \text{AVss} = 0 \text{ V}, \text{Reference voltage (+)} = 0.00 \text{ V}$ AVREFP, Reference voltage (-) = AVREFM = 0 V)

| Parameter | Symbol | Cond | litions | MIN. | TYP. | MAX. | Unit |
|--|----------------------|--|--------------------------------|--------|----------|------------------|---------|
| Resolution | Res | | $2.4~V \le AV_{DD} \le 3.6~V$ | 8 | | 12 | bit |
| | | | $1.8~V \le AVDD \le 3.6~V$ | 8 | | 10 Note 1 | |
| | | | $1.6~V \le AVDD \le 3.6~V$ | | 8 Note 2 | | |
| Overall error ^{Note 3} | AINL | 12-bit resolution | $2.4~V \le AV_{DD} \le 3.6~V$ | | | ±6.0 | LSB |
| | | 10-bit resolution | $1.8~V \le AVDD \le 3.6~V$ | | | ±3.5 | |
| | | 8-bit resolution | $1.6~V \le AV_{DD} \le 3.6~V$ | | | ±1.75 | |
| Conversion time | tconv | ADTYP = 0, 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | 3.375 | | | μS |
| | | ADTYP = 0, 10-bit resolution Note 1 | $1.8~V \leq V_{DD} \leq 3.6~V$ | 6.75 | | | |
| | | ADTYP = 0, 8-bit resolution Note 2 | $1.6~V \leq V_{DD} \leq 3.6~V$ | 13.5 | | | |
| | | 9 hit recolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | 2.5625 | | | |
| | | | $1.8~V \leq V_{DD} \leq 3.6~V$ | 5.125 | | | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 10.25 | | | |
| Zero-scale error ^{Notes 3, 4} | EZS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±4.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±2.5 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±1.25 | |
| Full-scale error ^{Notes 3, 4} | EFS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±4.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±2.5 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±1.25 | |
| Integral linearity errorNote 3 | ILE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Differential linearity error Note 3 | DLE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Reference voltage (+) | AV _{REF(+)} | = AVREFP | $2.4~V \leq V_{DD} \leq 3.6~V$ | 2.4 | | AV _{DD} | V |
| | | | $1.8~V \leq V_{DD} \leq 3.6~V$ | 1.8 | | AV _{DD} | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 1.6 | | AV _{DD} | |
| Reference voltage (-) | AV _{REF(-)} | = AVREFM | | -0.5 | | 0.3 | V |
| Analog input voltage | Vain | | | 0 | | AVREFP | V |
| | V _{BGR} | $2.4~V \leq V_{DD} \leq 3.6~V$ | | 1.38 | 1.45 | 1.5 | V |
| Consumption current | IADC | AVDD = 3.6 V | | 460 | 1090 | μΑ | |
| VREF current | IAVREF | AVREFP = 3.6 V | | | 14 | 25 | μ A |

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - 2. Cannot be used for lower 4 bit of ADCR register
 - **3.** Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



Specifications in this document are tentative and subject to change.

(2) When AVREF (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), AVREF (-) = AVSS (ADREFM = 0), target ANI pin : ANIO to ANI12 (supply ANI pin to AVDD)

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 3.6 V, 1.6 V \leq AVDD \leq 3.6 V, Vss = 0 V, AVss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

| Parameter | Symbol | Cond | litions | MIN. | TYP. | MAX. | Unit |
|--|---------------------|--|-------------------------------------|--------|----------|-----------|------|
| Resolution | Res | | $2.4~V \le AV_{DD} \le 3.6~V$ | 8 | | 12 | bit |
| | | | $1.8~V \le AV_{DD} \le 3.6~V$ | 8 | | 10 Note 1 | |
| | | | $1.6~V \le AV_{DD} \le 3.6~V$ | | 8 Note 2 | | |
| Overall error ^{Note 3} | AINL | 12-bit resolution | $2.4~V \le AV_{DD} \le 3.6~V$ | | | ±9.0 | LSB |
| | | 10-bit resolution | $1.8~V \le AVDD \le 3.6~V$ | | | ±5.0 | |
| | | 8-bit resolution | $1.6~V \le AVDD \le 3.6~V$ | | | ±2.5 | |
| Conversion time | tconv | ADTYP = 0, 12-bit resolution | $2.4~V \leq V \text{DD} \leq 3.6~V$ | 3.375 | | | μS |
| | | ADTYP = 0, 10-bit resolution Note 1 | $1.8~V \leq V \text{DD} \leq 3.6~V$ | 6.75 | | | |
| | | ADTYP = 0, 8-bit resolution Note 2 | $1.6~V \leq V \text{DD} \leq 3.6~V$ | 13.5 | | | |
| | | ADTYP = 1, | $2.4~V \leq V_{DD} \leq 3.6~V$ | 2.5625 | | | |
| | | 8-bit resolution | 1.8 V ≤ VDD ≤ 3.6 V | 5.125 | | | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 10.25 | | | |
| Zero-scale error ^{Notes 3, 4} | EZS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±7.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±3.75 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.0 | |
| Full-scale error ^{Notes 3, 4} | EFS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±7.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±3.75 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.0 | |
| Integral linearity error ^{Note 3} | ILE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Differential linearity error Note 3 | DLE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Reference voltage (+) | AVREFP | = AVDD | | 1.6 | | 3.6 | V |
| Reference voltage (-) | AVREFM | = AVss | | -0.5 | | 0.3 | V |
| Analog input voltage | nalog input voltage | | | 0 | | AVREFP | V |
| | V _{BGR} | $2.4 \text{ V} \le \text{Vdd} \le 3.6 \text{ V}$ | | 1.38 | 1.45 | 1.5 | V |
| Consumption current | IADC | AVDD = 3.6 V | | 460 | 1090 | μΑ | |
| V _{REF} current | IAVREF | AVREFP = 3.6 V | | | 14 | 25 | μΑ |

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - Cannot be used for lower 4 bit of ADCR register
 - Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



Specifications in this document are tentative and subject to change.

(3) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI16 to ANI30 (supply ANI pin to EVDDO)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \text{ V} \le \text{EV}_{\text{DD}} \le \text{V}_{\text{DD}} \le 3.6 \text{ V}, \ 1.6 \text{ V} \le \text{AV}_{\text{DD}} \le 3.6 \text{ V}, \ \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = 0 \text{ V}, \ \text{AV}_{\text{SS}} = 0 \text{ V}, \ \text{Reference}$ voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

| Parameter | Symbol | Cond | litions | MIN. | TYP. | MAX. | Unit |
|--|-----------------------|--|-------------------------------------|--------|----------|------------------|------|
| Resolution | Res | | $2.4~V \le AV_{DD} \le 3.6~V$ | 8 | | 12 | bit |
| | | | $1.8~V \leq AV_{DD} \leq 3.6~V$ | 8 | | 10 Note 1 | |
| | | | $1.6~V \le AV_{DD} \le 3.6~V$ | | 8 Note 2 | | |
| Overall error ^{Note 3} | AINL | 12-bit resolution | $2.4~V \le AV_{DD} \le 3.6~V$ | | | ±9.0 | LSB |
| | | 10-bit resolution | $1.8~V \le AVDD \le 3.6~V$ | | | ±5.0 | |
| | | 8-bit resolution | $1.6~V \le AV_{DD} \le 3.6~V$ | | | ±2.5 | |
| Conversion time | tconv | ADTYP = 0, 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | 4.125 | | | μS |
| | | ADTYP = 0, 10-bit resolution Note 1 | $1.8~V \leq V_{DD} \leq 3.6~V$ | 9.5 | | | |
| | | ADTYP = 0, 8-bit resolution Note 2 | $1.6~V \leq V \text{DD} \leq 3.6~V$ | 57.5 | | | |
| | | ADTYP = 1, | $2.4~V \leq V_{DD} \leq 3.6~V$ | 3.3125 | | | |
| | | 8-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | 7.875 | | | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 54.25 | | | |
| Zero-scale error ^{Notes 3, 4} | EZS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±7.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±3.75 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.0 | |
| Full-scale error ^{Notes 3, 4} | EFS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±7.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±3.75 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.0 | |
| Integral linearity error ^{Note 3} | ILE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Differential linearity error Note 3 | DLE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Reference voltage (+) | AV _{REF(+)} | = AVREFP | $2.4~V \leq V_{DD} \leq 3.6~V$ | 2.4 | | AV _{DD} | V |
| | | | $1.8~V \leq V_{DD} \leq 3.6~V$ | 1.8 | | AV _{DD} | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 1.6 | | AV _{DD} | |
| Reference voltage (-) | AV _{REF((-)} | = AVREFM | | -0.5 | | 0.3 | ٧ |
| Analog input voltage | Vain | 2.4 V ≤ VDD ≤ 3.6 V | | 0 | | AVREFP | ٧ |
| | V _{BGR} | | | 1.38 | 1.45 | 1.5 | ٧ |
| Consumption current | IADC | AVDD = 3.6 V | | 400 | 950 | μА | |
| V _{REF} current | IAVREF | AVREFP = 3.6 V | | | 14 | 25 | μΑ |

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - 2. Cannot be used for lower 4 bit of ADCR register
 - **3.** Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



Specifications in this document are tentative and subject to change.

(4) When AVREF (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), AVREF (-) = AVSS (ADREFM = 0), target ANI pin : ANI16 to ANI30 (supply ANI pin to EVDDO)

 $(T_{\text{A}} = -40 \text{ to } +85^{\circ}\text{C}, \ 1.6 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq \text{V}_{\text{DD0}} \leq 3.6 \ \text{V}, \ 1.6 \ \text{V} \leq \text{AV}_{\text{DD}} \leq 3.6 \ \text{V}, \ \text{Vss} = \text{EV}_{\text{SS0}} = 0 \ \text{V}, \ \text{AVss} = 0 \ \text{V}, \ \text{Reference} = 0 \ \text{V}$ voltage (+) = AVDD, Reference voltage (-) = AVss = 0 V)

| Parameter | Symbol | Cond | litions | MIN. | TYP. | MAX. | Unit |
|--|----------------------|--|-------------------------------------|--------|----------|-----------|------|
| Resolution | Res | | $2.4~V \le AV_{DD} \le 3.6~V$ | 8 | | 12 | bit |
| | | | $1.8~V \le AV_{DD} \le 3.6~V$ | 8 | | 10 Note 1 | |
| | | | 1.6 V ≤ AVDD ≤ 3.6 V | | 8 Note 2 | | |
| Overall error ^{Note 3} | AINL | 12-bit resolution | $2.4~V \le AV_{DD} \le 3.6~V$ | | | ±14.0 | LSB |
| | | 10-bit resolution | $1.8~V \le AVDD \le 3.6~V$ | | | ±7.5 | |
| | | 8-bit resolution | $1.6~V \le AVDD \le 3.6~V$ | | | ±3.75 | |
| Conversion time | tconv | ADTYP = 0, 12-bit resolution | $2.4~V \leq V \text{DD} \leq 3.6~V$ | 4.125 | | | μS |
| | | ADTYP = 0, 10-bit resolution Note 1 | $1.8~V \leq V \text{DD} \leq 3.6~V$ | 9.5 | | | |
| | | ADTYP = 0, 8-bit resolution Note 2 | $1.6~V \leq V \text{DD} \leq 3.6~V$ | 57.5 | | | |
| | | ADTYP = 1, | $2.4~V \leq V_{DD} \leq 3.6~V$ | 3.3125 | | | μS |
| | | 8-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | 7.875 | | | |
| | | | $1.6~V \leq V_{DD} \leq 3.6~V$ | 54.25 | | | |
| Zero-scale error ^{Notes 3, 4} | EZS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±9.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±5.0 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.5 | |
| Full-scale error ^{Notes 3, 4} | EFS | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | ±9.0 | %FSR |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | ±5.0 | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | ±2.5 | |
| Integral linearity error ^{Note 3} | ILE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Differential linearity error Note 3 | DLE | 12-bit resolution | $2.4~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | LSB |
| | | 10-bit resolution | $1.8~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| | | 8-bit resolution | $1.6~V \leq V_{DD} \leq 3.6~V$ | | | T.B.D. | |
| Reference voltage (+) | AV _{REF(+)} | = AVDD | | 1.6 | | 3.6 | V |
| Reference voltage (-) | AVREF(-) | = AVss | | -0.5 | | 0.3 | V |
| Analog input voltage | Vain | | | 0 | | AVREFP | V |
| | V _{BGR} | 2.4 V ≤ VDD ≤ 3.6 V | | 1.38 | 1.45 | 1.5 | V |
| Consumption current | IADC | AVDD = 3.6 V | | 400 | 950 | μΑ | |
| VREF current | lavref | AVREFP = 3.6 V | | | 14 | 25 | μΑ |

- Notes 1. Cannot be used for lower 2 bit of ADCR register
 - 2. Cannot be used for lower 4 bit of ADCR register
 - Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.



(5) When AVREF (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), AVREF (-) = AVss (ADREFM = 0), target ANI pin : ANI0 to ANI12, ANI16 to ANI30

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 3.6 V, 1.6 V \leq AVDD \leq 3.6 V, Vss = EVss0 = 0 V, AVss0 = 0 V, Reference voltage (+) = Internal reference voltage, Reference voltage (-) = AVss = 0 V)

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|----------------------|------------------------------|---------------------|------|--------|------|
| Resolution | RES | | | 8 | | bit |
| Conversion time | tconv | 8-bit resolution | 16 | | | μS |
| Zero-scale error ^{Notes 1, 2} | EZS | 8-bit resolution | | | ±2.5 | %FSR |
| Integral linearity error ^{Note 1} | ILE | 8-bit resolution | | | T.B.D. | LSB |
| Differential linearity error Note 1 | DLE | 8-bit resolution | | | T.B.D. | LSB |
| Reference voltage (+) | AV _{REF(+)} | = Internal reference voltage | 1.38 | 1.45 | 1.5 | ٧ |
| Reference voltage (-) | AV _{REF(-)} | = AVss | -0.5 | | 0.3 | ٧ |
| Analog input voltage | VAIN | | 0 | | AVREFP | ٧ |
| | V _{BGR} | | Conversion prohibit | | | V |
| Consumption current | IADC | AVDD = 3.6 V | | 400 | 950 | μΑ |
| VREF current | lavref | | | 75 | | μΑ |

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

^{2.} This value is indicated as a ratio (%FSR) to the full-scale value.

2.6.2 Temperature sensor characteristics

(Ta = -40 to +85°C, 2.4 V \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-----------------------------------|---------------------|--|------|------|------|------|
| Temperature sensor output voltage | V _{TMPS25} | Setting ADS register = 80H, Ta = +25°C | | 1.05 | | V |
| Reference output voltage | VCONST | Setting ADS register = 81H | 1.38 | 1.45 | 1.5 | V |
| Temperature coefficient | FVTMPS | Temperature sensor that depends on the temperature | | -3.6 | | mV/C |
| Operation stabilization wait time | tamp | | | | 2 | μS |

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|----------------------|------------------|------------------------|------|------|------|------|
| Detection voltage | VPOR | Power supply rise time | | 1.51 | 1.54 | V |
| | V _{PDR} | Power supply fall time | 1.47 | 1.50 | 1.53 | ٧ |
| Minimum pulse width | T _{PW} | | 300 | | | μS |
| Detection delay time | | | | | 350 | μS |

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{PDR} \le EV_{DD0} \le V_{DD} \le 3.6 \text{ V}, V_{SS} = EV_{SS0} = 0 \text{ V})$

| | Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------|----------------------|------------------------|------------------------|------|------|------|------|
| Detection | Supply voltage level | V _{LVD2} | Power supply rise time | 3.07 | 3.13 | 3.19 | V |
| voltage | | | Power supply fall time | 3.00 | 3.06 | 3.12 | V |
| | | V LVD3 | Power supply rise time | 2.96 | 3.02 | 3.08 | ٧ |
| | | | Power supply fall time | 2.90 | 2.96 | 3.02 | V |
| | | V _{LVD4} | Power supply rise time | 2.86 | 2.92 | 2.97 | V |
| | | Power supply fall time | 2.80 | 2.86 | 2.91 | V | |
| | V _{LVD5} | Power supply rise time | 2.76 | 2.81 | 2.87 | V | |
| | | | Power supply fall time | 2.70 | 2.75 | 2.81 | V |
| | | V _{LVD6} | Power supply rise time | 2.66 | 2.71 | 2.76 | V |
| | | Power supply fall time | 2.60 | 2.65 | 2.70 | V | |
| | V LVD7 | Power supply rise time | 2.56 | 2.61 | 2.66 | ٧ | |
| | | Power supply fall time | 2.50 | 2.55 | 2.60 | V | |
| | V _{LVD8} | Power supply rise time | 2.45 | 2.50 | 2.55 | V | |
| | | | Power supply fall time | 2.40 | 2.45 | 2.50 | V |
| | | V _{LVD9} | Power supply rise time | 2.05 | 2.09 | 2.13 | V |
| | | | Power supply fall time | 2.00 | 2.04 | 2.08 | V |
| | | V _{LVD10} | Power supply rise time | 1.94 | 1.98 | 2.02 | V |
| | | | Power supply fall time | 1.90 | 1.94 | 1.98 | V |
| | | V _{LVD11} | Power supply rise time | 1.84 | 1.88 | 1.91 | V |
| | | | Power supply fall time | 1.80 | 1.84 | 1.87 | V |
| | | V _{LVD12} | Power supply rise time | 1.74 | 1.77 | 1.81 | V |
| | | | Power supply fall time | 1.70 | 1.73 | 1.77 | V |
| | | V _{LVD13} | Power supply rise time | 1.64 | 1.67 | 1.70 | V |
| | | | Power supply fall time | 1.60 | 1.63 | 1.66 | V |
| Minimum pı | ulse width | tLW | | 300 | | | μS |
| Detection d | elay time | | | | | 300 | μS |

Remark $V_{LVD(n-1)} > V_{LVDn}$: n = 3 to 13



LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 3.6 V, Vss = EVss0 = 0 V)

| Parameter | Symbol | | Cond | litions | MIN. | TYP. | MAX. | Unit |
|---------------------|--------------------|-------------------|---------------------------------|--------------------------------|------|------|------|------|
| Interrupt and reset | V _{LVD13} | V _{POC0} | VPOC1, VPOC2 = 0, 0, 0 | , falling reset voltage: 1.6 V | 1.60 | 1.63 | 1.66 | V |
| mode | V _{LVD12} | | LVIS0, LVIS1 = 1, 0 | Rising release reset voltage | 1.74 | 1.77 | 1.81 | V |
| | | | (+0.1 V) | Falling interrupt voltage | 1.70 | 1.73 | 1.77 | V |
| | V _{LVD11} | | LVIS0, LVIS1 = 0, 1 | Rising release reset voltage | 1.84 | 1.88 | 1.91 | V |
| | | | (+0.2 V) | Falling interrupt voltage | 1.80 | 1.84 | 1.87 | V |
| | V _{LVD4} | | LVIS0, LVIS1 = 0, 0 | Rising release reset voltage | 2.86 | 2.92 | 2.97 | V |
| | | | (+1.2 V) | Falling interrupt voltage | 2.80 | 2.86 | 2.91 | V |
| | V _{LVD11} | V _{POC0} | VPOC1, VPOC2 = 0, 0, 1 | , falling reset voltage: 1.8 V | 1.80 | 1.84 | 1.87 | V |
| | V _{LVD10} | | LVIS0, LVIS1 = 1, 0 | Rising release reset voltage | 1.94 | 1.98 | 2.02 | V |
| | | | (+0.1 V) | Falling interrupt voltage | 1.90 | 1.94 | 1.98 | V |
| | V _{LVD9} | | 1 ' - | Rising release reset voltage | 2.05 | 2.09 | 2.13 | V |
| | | (+ | (+0.2 V) | Falling interrupt voltage | 2.00 | 2.04 | 2.08 | V |
| | V _{LVD2} | | LVIS0, LVIS1 = 0, 0 (+1.2 V) | Rising release reset voltage | 3.07 | 3.13 | 3.19 | V |
| | | | | Falling interrupt voltage | 3.00 | 3.06 | 3.12 | V |
| | V _{LVD8} | V _{POC0} | VPOC1, VPOC2 = 0, 1, 0 | , falling reset voltage: 2.4 V | 2.40 | 2.45 | 2.50 | ٧ |
| | V LVD7 | | LVIS0, LVIS1 = 1, 0 | Rising release reset voltage | 2.56 | 2.61 | 2.66 | V |
| | | | (+0.1 V) | Falling interrupt voltage | 2.50 | 2.55 | 2.60 | V |
| | V _{LVD6} | | LVIS0, LVIS1 = 0, 1 | Rising release reset voltage | 2.66 | 2.71 | 2.76 | V |
| | | | (+0.2 V) | Falling interrupt voltage | 2.60 | 2.65 | 2.70 | V |
| | V _{LVD5} | V _{POC0} | VPOC1, VPOC2 = 0, 1, 1, | , falling reset voltage: 2.7 V | 2.70 | 2.75 | 2.81 | V |
| | V _{LVD4} | | LVIS0, LVIS1 = 1, 0 | Rising release reset voltage | 2.86 | 2.92 | 2.97 | ٧ |
| | | | (+0.1 V) | Falling interrupt voltage | 2.80 | 2.86 | 2.91 | ٧ |
| | V LVD3 | V _{LVD3} | | Rising release reset voltage | 2.96 | 3.02 | 3.08 | ٧ |
| | | | (+0.2 V) | Falling interrupt voltage | 2.90 | 2.96 | 3.02 | ٧ |

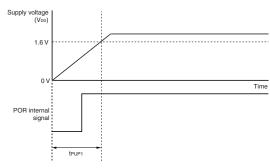
Supply Voltage Rise Time ($T_A = -40 \text{ to } +85^{\circ}\text{C}$, $V_{SS} = 0 \text{ V}$)

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|--------|------------------------------|------|------|------|------|
| Maximum time to rise to 1.6 V (V _{DD} (MIN.)) ^{Note} (V _{DD} : 0 V \rightarrow 1.6 V) | tpup1 | When RESET input is not used | | | 3.2 | ms |

Note Make sure to raise the power supply in a shorter time than this.

Supply Voltage Rise Time Timing

• When RESET pin input is not used

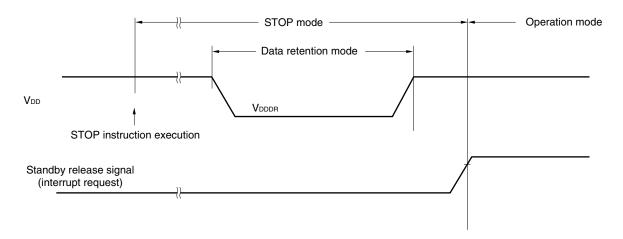


2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------|-------------------|------------|----------------------|------|------|------|
| Data retention supply voltage | V _{DDDR} | | 1.47 ^{Note} | | 3.6 | ٧ |

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} < \text{FV}_{DDO} < V_{DD} < 3.6 \text{ V}, V_{SS} = \text{FV}_{SSO} = 0 \text{ V})$

| $(1A = -40 10 +65 C, 1.6 V \le E)$ | 1 DOU - V D | D <u> </u> | 0 – 0 v) | | | | |
|---|-------------|---|--|---------|-----------|------|-------|
| Parameter | Symbol | Cond | MIN. | TYP. | MAX. | Unit | |
| CPU/peripheral hardware clock frequency | fclk | $1.8~V \leq V_{DD} \leq 3.6~V$ | | 1 | | 32 | MHz |
| Number of code flash rewrites | Cerwr | 1 erase + 1 write after the erase is regarded as 1 rewrite. | Retained for 20 years (Self/serial programming) Note | 1,000 | | | Times |
| Number of data flash rewrites | | The retaining years are until next rewrite after the rewrite. | Retained for 1 years (Self/serial programming) Note | | 1,000,000 | | |
| | | | Retained for 5 years (Self/serial programming) Note | 100,000 | | | |

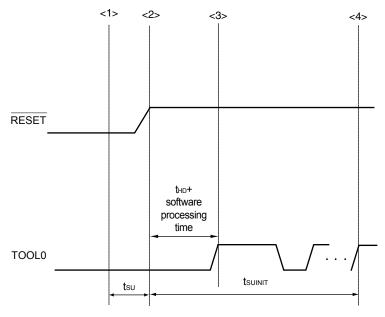
Note When using flash memory programmer and Renesas Electronics self programming library

Remark When updating data multiple times, use the flash memory as one for updating data.

2.9 Timing Specs for Switching Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$

| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|--|---------|---|------|------|------|------|
| How long from when a pin reset ends until the initial communication settings are specified | tsuinit | POR and LVD reset must end before the pin reset ends. | | | 100 | ms |
| How long from when the TOOL0 pin is placed at the low level until a pin reset ends | tsu | POR and LVD reset must end before the pin reset ends. | 10 | | | μS |
| How long the TOOL0 pin must be kept at the low level after a reset ends | thd | POR and LVD reset must end before the pin reset ends. | 1 | | | ms |



- <1> The low level is input to the TOOL0 pin.
- <2> The pins reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external and internal resets end.

How long from when the TOOL0 pin is placed at the low level until a pin reset ends tsu:

How long to keep the TOOL0 pin at the low level from when the external and internal resets end tHD:

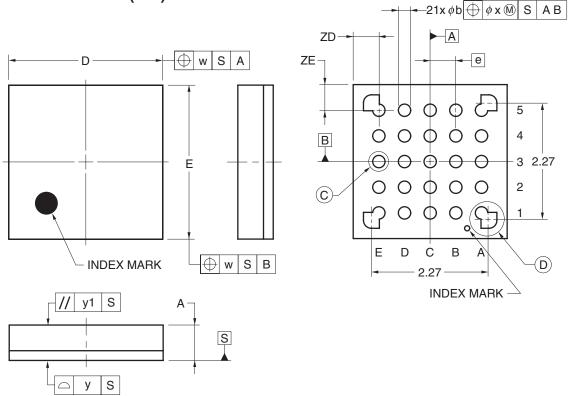
3. PACKAGE DRAWINGS

3.1 25-pin products

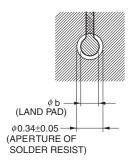
R5F10E8AALA, R5F10E8CALA, R5F10E8DALA, R5F10E8EALA

Specifications in this document are tentative and subject to change.

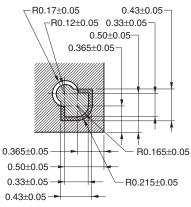
25-PIN PLASTIC FLGA (3x3)







DETAIL OF (D) PART



| | (UNIT:mm) |
|------|----------------|
| ITEM | DIMENSIONS |
| D | 3.00±0.10 |
| Е | 3.00±0.10 |
| W | 0.20 |
| е | 0.50 |
| Α | 0.69±0.07 |
| b | 0.24±0.05 |
| х | 0.05 |
| У | 0.08 |
| y1 | 0.20 |
| ZD | 0.50 |
| ZE | 0.50 |
| | P25FC-50-2N2-1 |

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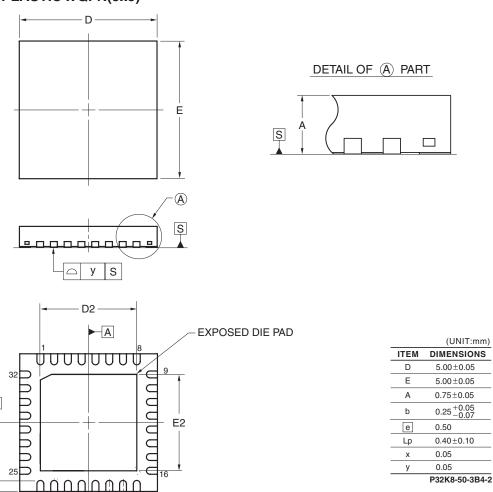
3.2 32-pin products

R5F10EBAANA, R5F10EBCANA, R5F10EBDANA, R5F10EBEANA

b x M S A B

Specifications in this document are tentative and subject to change.

32-PIN PLASTIC WQFN(5x5)



| ITEM | | D2 | | | E2 | | |
|----------------------------------|---|------|------|------|------|------|------|
| | | MIN | NOM | MAX | MIN | NOM | MAX |
| EXPOSED DIE PAD VARIATIONS | Α | 3.45 | 3.50 | 3.55 | 3.45 | 3.50 | 3.55 |

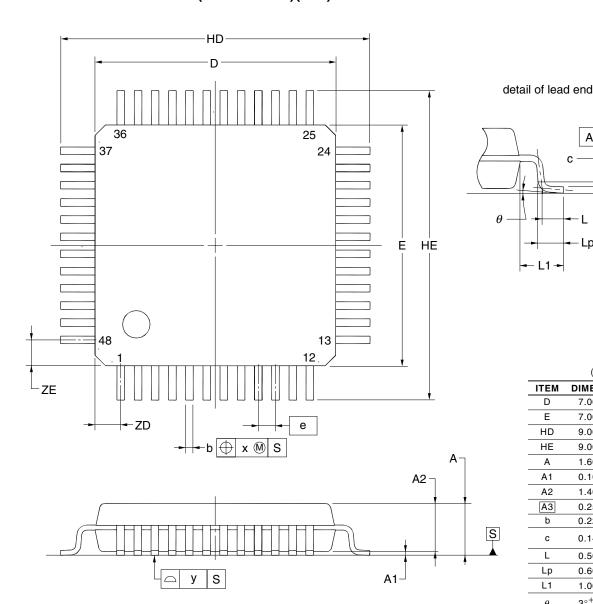
АЗ

3.3 48-pin products

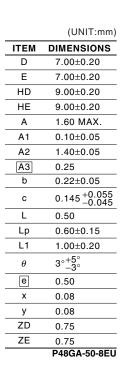
R5F10EGAAFB, R5F10EGCAFB, R5F10EGDAFB, R5F10EGEAFB

Specifications in this document are tentative and subject to change.

48-PIN PLASTIC LQFP (FINE PITCH)(7x7)



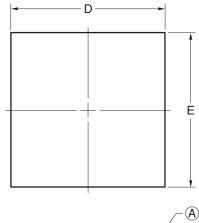
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

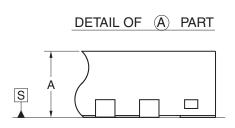


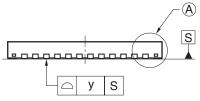
R5F10EGAANA, R5F10EGCANA, R5F10EGDANA, R5F10EGEANA

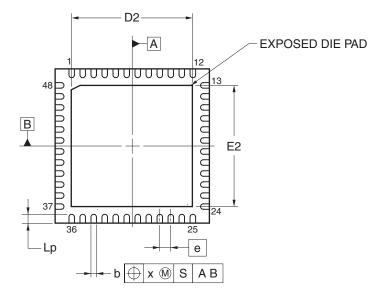
Specifications in this document are tentative and subject to change.

48-PIN PLASTIC WQFN(7x7)









| | (UNIT:mm) |
|------|--|
| ITEM | DIMENSIONS |
| D | 7.00 ± 0.05 |
| Е | 7.00 ± 0.05 |
| Α | 0.75±0.05 |
| b | 0.25 ^{+0.05} _{-0.07} |
| е | 0.50 |
| Lp | 0.40±0.10 |
| х | 0.05 |
| у | 0.05 |
| | P48K8-50-5B4-3 |

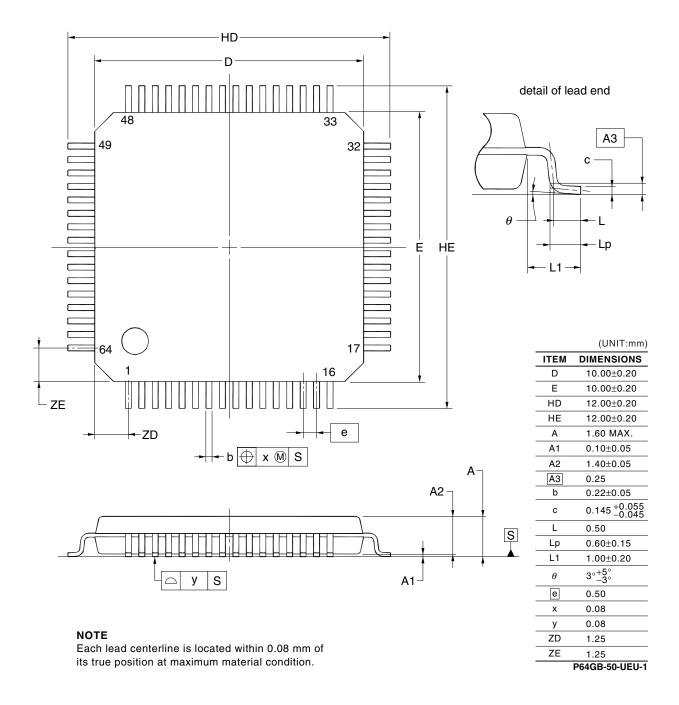
| ITFM | | D2 | | | E2 | | |
|----------------------------------|---|------|------|------|------|------|------|
| | | MIN | NOM | MAX | MIN | MON | MAX |
| EXPOSED DIE PAD VARIATIONS | Α | 5.45 | 5.50 | 5.55 | 5.45 | 5.50 | 5.55 |

Specifications in this document are tentative and subject to change.

3.4 64-pin products

R5F10ELCAFB, R5F10ELDAFB, R5F10ELEAFB

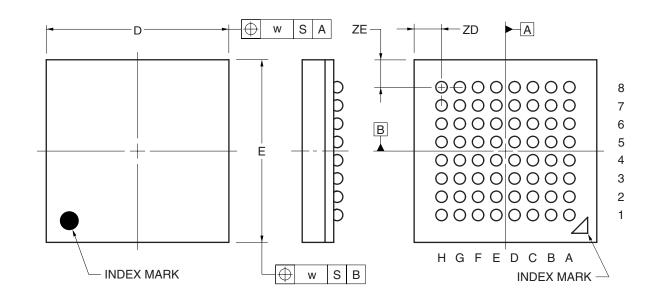
64-PIN PLASTIC LQFP(FINE PITCH)(10x10)

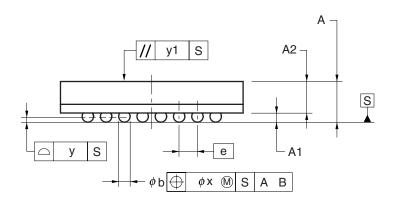


Specifications in this document are tentative and subject to change.

R5F10ELCABG, R5F10ELDABG, R5F10ELEABG

64-PIN PLASTIC FBGA (4x4)





| | (UNIT:mm) |
|------|----------------|
| ITEM | DIMENSIONS |
| D | 4.00±0.10 |
| E | 4.00±0.10 |
| W | 0.15 |
| Α | 0.89±0.10 |
| A1 | 0.20±0.05 |
| A2 | 0.69 |
| е | 0.40 |
| b | 0.25±0.05 |
| х | 0.05 |
| у | 0.08 |
| y1 | 0.20 |
| ZD | 0.60 |
| ZE | 0.60 |
| | P64F1-40-AA2-1 |

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Revision History RL78/G1A Data Sheet

| | | Description | | | |
|------|--------------|-------------|----------------------|--|--|
| Rev. | Date | Page | Summary | | |
| 0.01 | Dec 26, 2011 | - | First Edition issued | | |
| | | | | | |

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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enesas Electronics America Inc. 80 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. d: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited Dukes Meadow, Millboard Road, Boume End, Buckinghamshire, SL8 5FH, U.K Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-2035-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No. 1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-5887-7589

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852-2886-9022/9044

Renesas Electronics Taiwan Co., Ltd. 7F, No. 363 Fu Shing North Road Taipei, Taiwa Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 1 harbourFront Avenue, #06-10, keppel Bay Tower, Singapore 098632 Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax-+60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bidg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2-558-3737, Fax: 482-2-558-5141

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